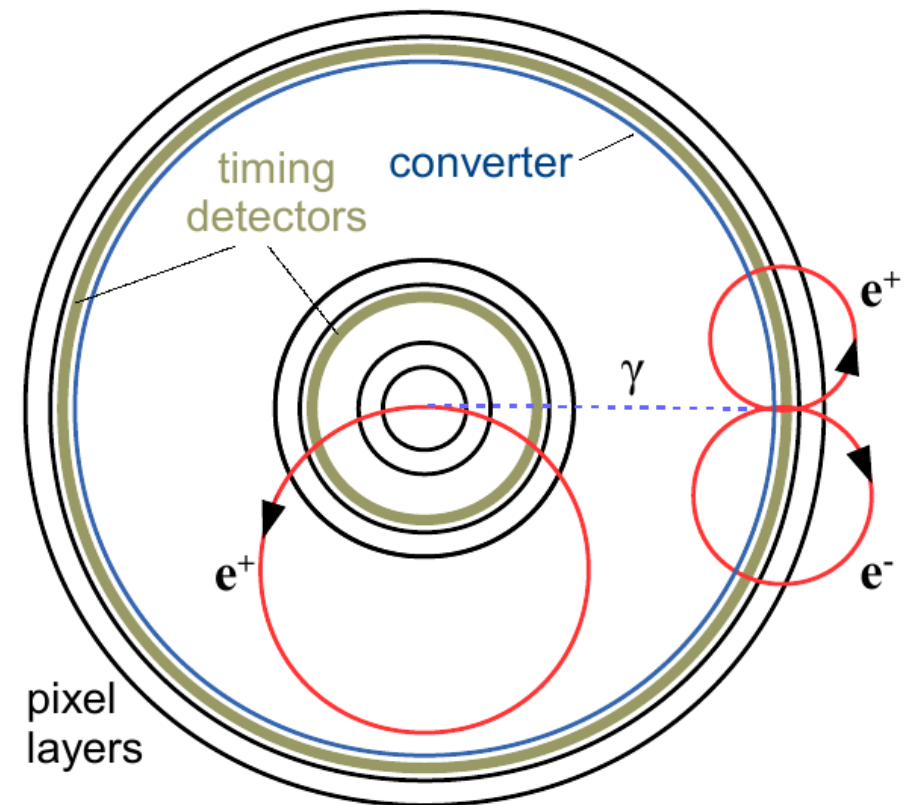


Status of Detector R&D for an All Silicon $\mu^+ \rightarrow e^+ \gamma$ Pixel Detector

Meeting on Future $\mu^+ \rightarrow e^+ \gamma$

A.Schöning

University Heidelberg, Physics Institute



Taken from HIMB case study

All Silicon Pixel Tracker for $\mu^+ \rightarrow e^+ \gamma$

$$\frac{N_{acc}}{N_{sig}} \stackrel{\text{def}}{=} B_{acc} \propto R_{\mu} \sigma(p_e) \sigma(E_{\gamma})^2 \sigma(\Theta_{e\gamma})^2 \sigma_{t_{e\gamma}}$$

- **Positron Tracker (incl. Vertex Detector)**

- high rate tolerance (+++)
- good vertex resolution (+++)

- **Ultra-Fast Silicon Pixel Detector (UFSPD)**

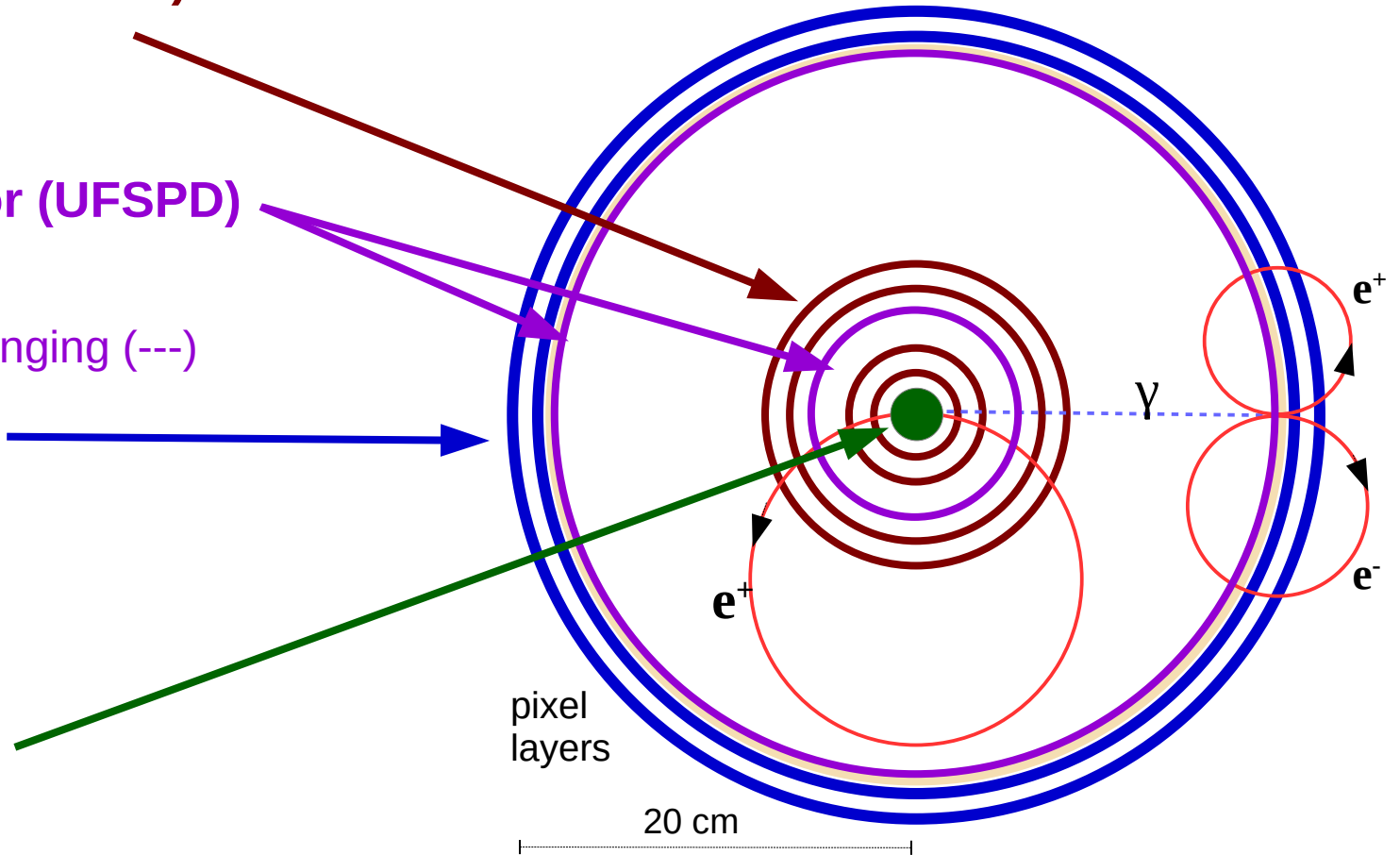
- thin HVMAPS possible (+++)
- time resolution <100 ps very challenging (---)

- **Converted Photon Tracker**

- high spatial resolution (+++)
- good directional resolution (+++)
- low efficiency (---)

- **Active Muon Stopping Target**

- precise decay vertex (+++)
- technologically challenging (---)



→ **Concept allows for high muon-stopping rates (R_{μ})**

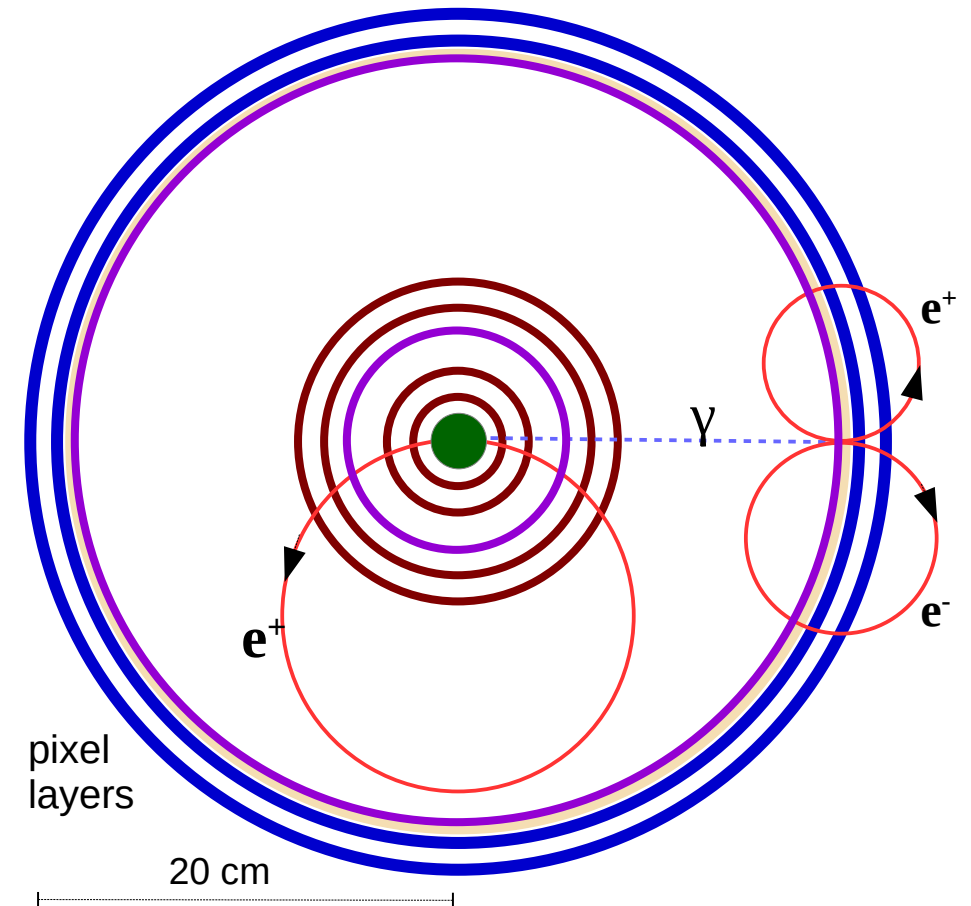
→ **high single event sensitivity (SES)**

All Silicon Pixel Tracker for $\mu^+ \rightarrow e^+ \gamma$

$$\frac{N_{acc}}{N_{sig}} \stackrel{\text{def}}{=} B_{acc} \propto R_{\mu} \sigma(p_e) \sigma(E_{\gamma})^2 \sigma(\Theta_{e\gamma})^2 \sigma_{t_{e\gamma}}$$

Ongoing Detector R&D in Heidelberg:

- Positron measurement
 - **thin** HVMAPS vertex layer
- **Ultra-Fast** Silicon Pixel Detector (\rightarrow timing)
- Photon measurement
 - Development of **thick HVMAPS converter**
 - Measurement of **in-situ** ionisation loss in silicon
- Overall Design
 - Mu3e-Gamma Concept
 - **Positron momentum resolution**

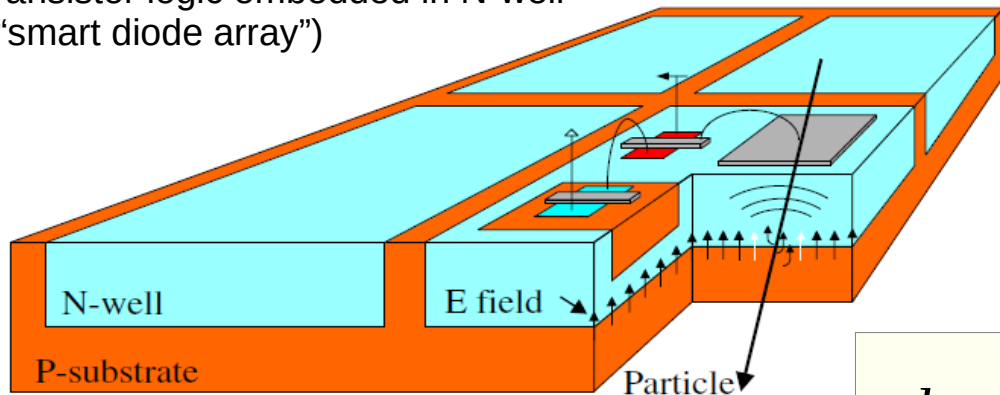


Very Challenging Detector Design!

High Voltage Active Monolithic Pixel Sensors

High Voltage-Monolithic Active Pixel Sensor (HV-MAPS)

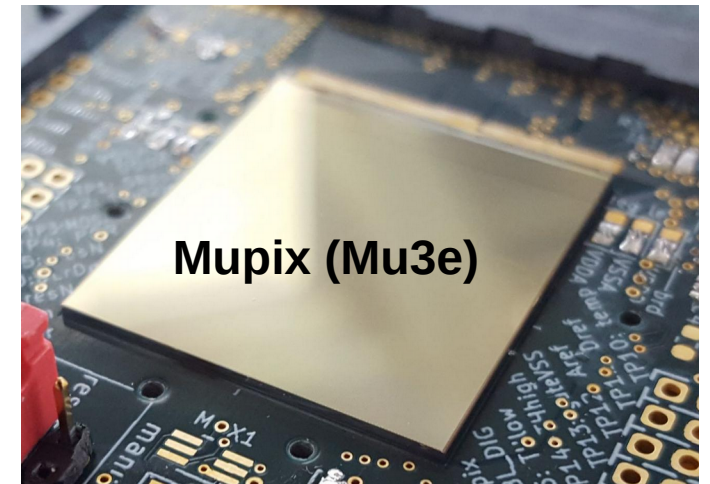
transistor logic embedded in N-well
("smart diode array")



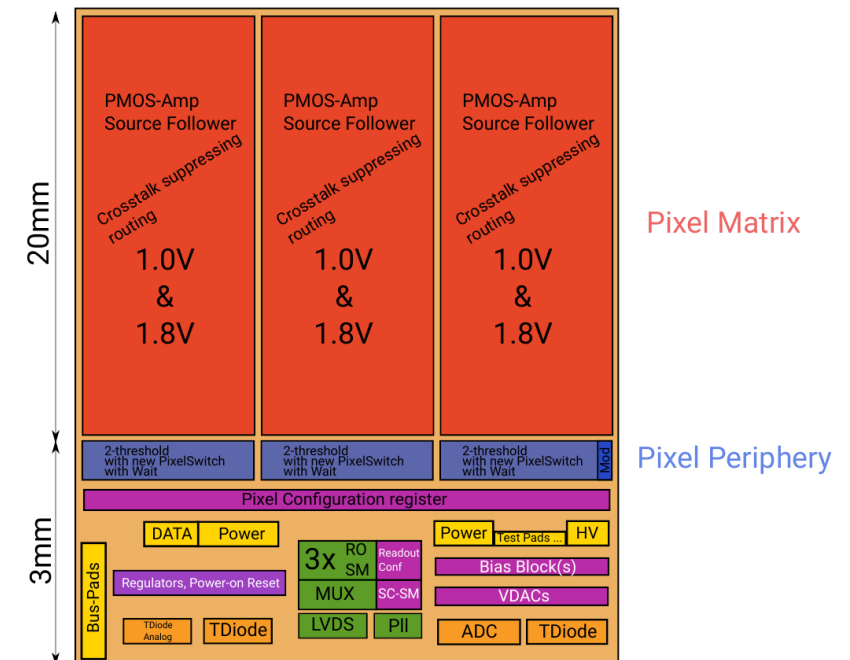
$$d_{depletion} \propto \sqrt{U_{bias} \rho}$$

I.Peric et al., NIM A 582 (2007) 876

- **fully monolithic: hit detection + digitisation + readout**
- 180nm HV-CMOS process
- "low" cost
- capable of high hit rates and fast readout
- can be thinned to **~50 μm** ($\sim 0.0005 X_0$)



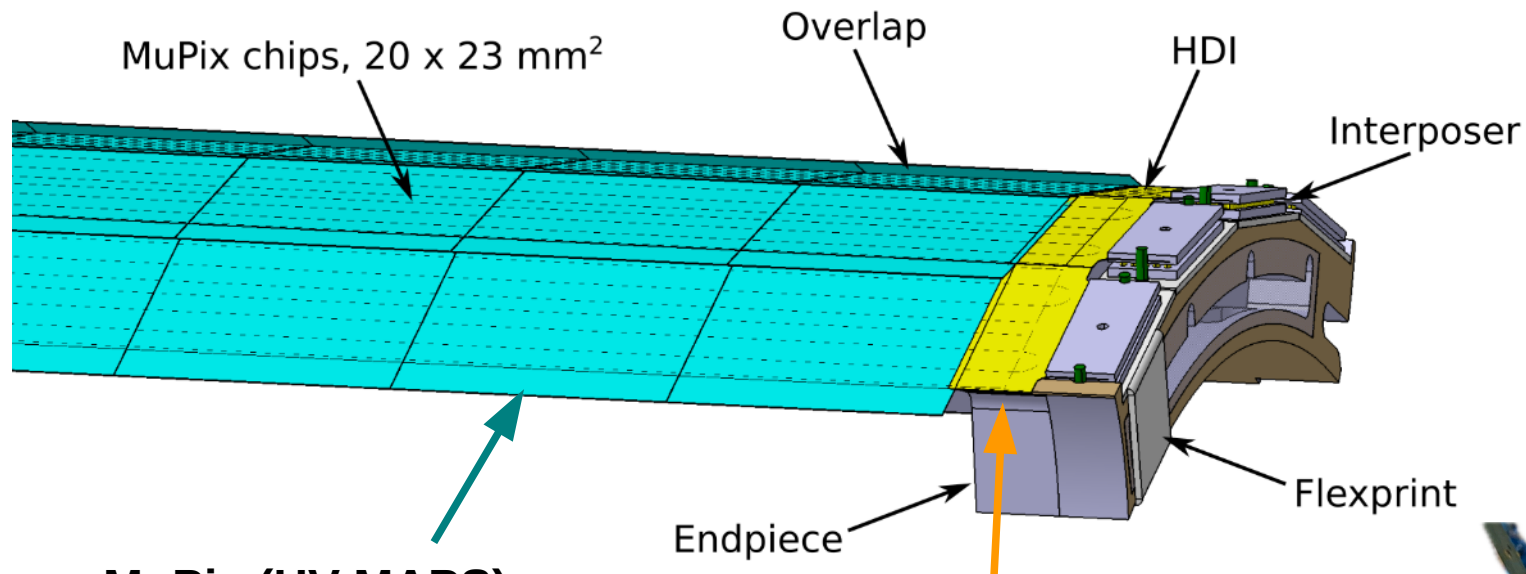
sensor: 20 x 20 mm² pixel: 80 x 80 μm^2



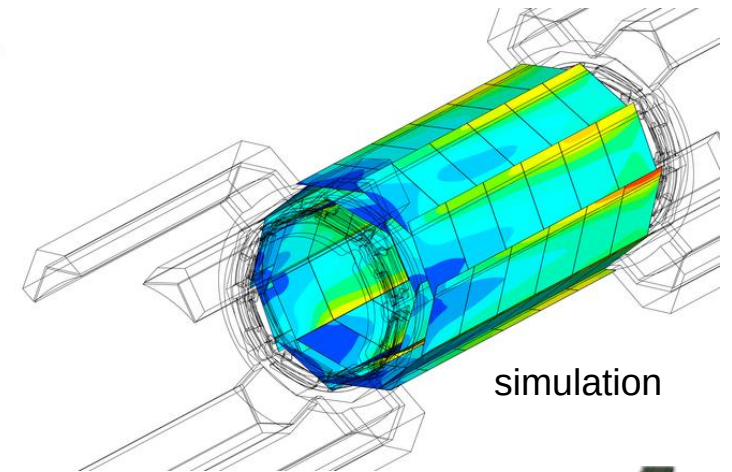
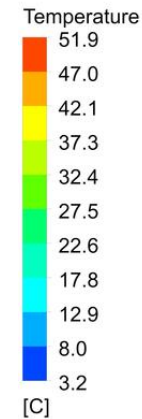


HVMAPS Tracking Detector (Mu3e)

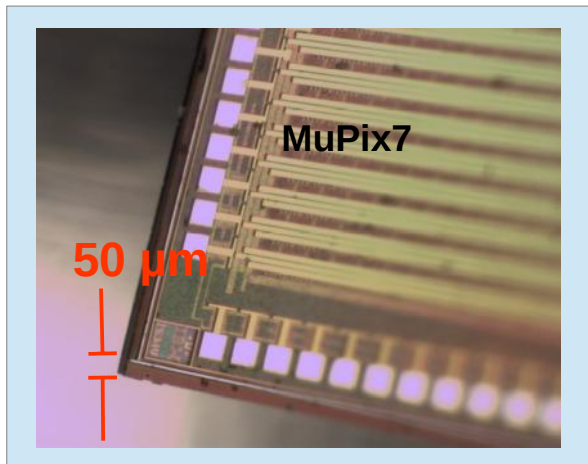
Ultra-thin pixel sensor modules ($X/X_0 = 1.15$ per mille)



Gaseous He-Cooling System

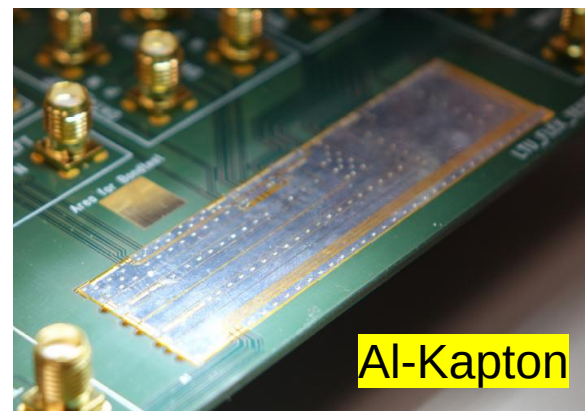


MuPix (HV-MAPS)

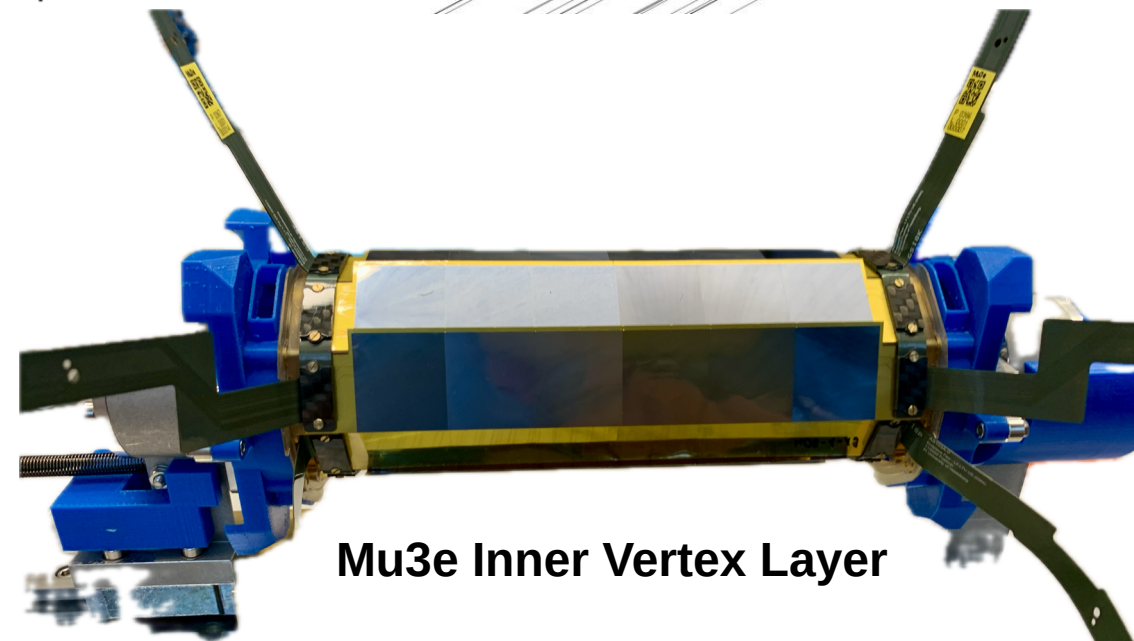


Monolithic pixel sensor in 180 nm HV-CMOS

High Density Interconnect d < 100 μm (LTU, Ukraine)



connectivity: spTAB method

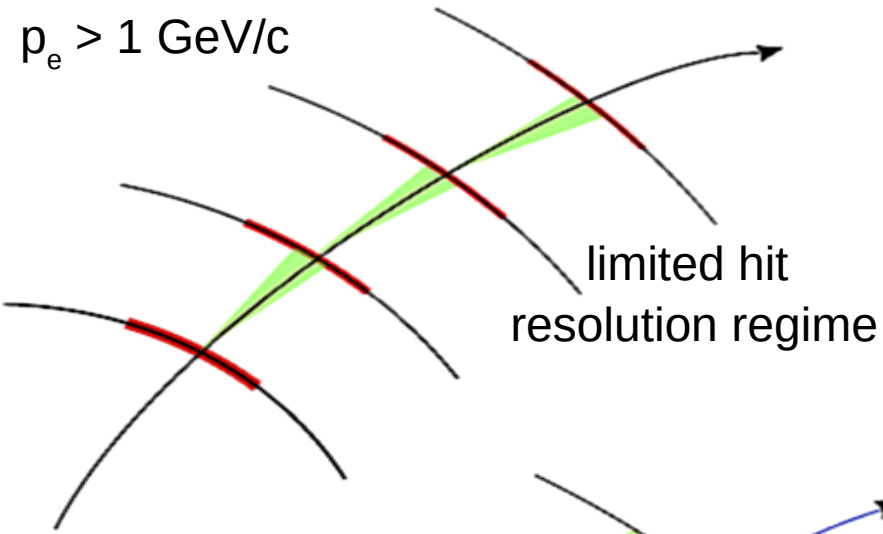


Mu3e Inner Vertex Layer

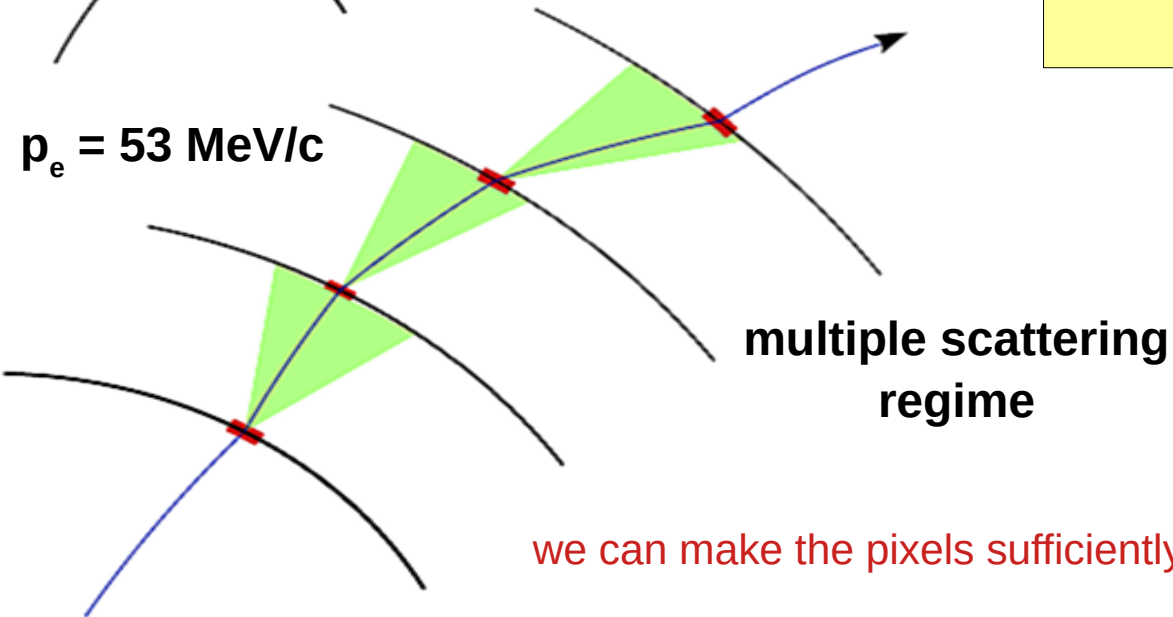
Silicon Pixel Vertex Detector

$$B_{acc} \propto R_{\mu} \sigma(p_e) \sigma(E_{\gamma})^2 \sigma(\Theta_{e\gamma})^2 \sigma_{t_{e\gamma}}$$

$p_e > 1 \text{ GeV}/c$



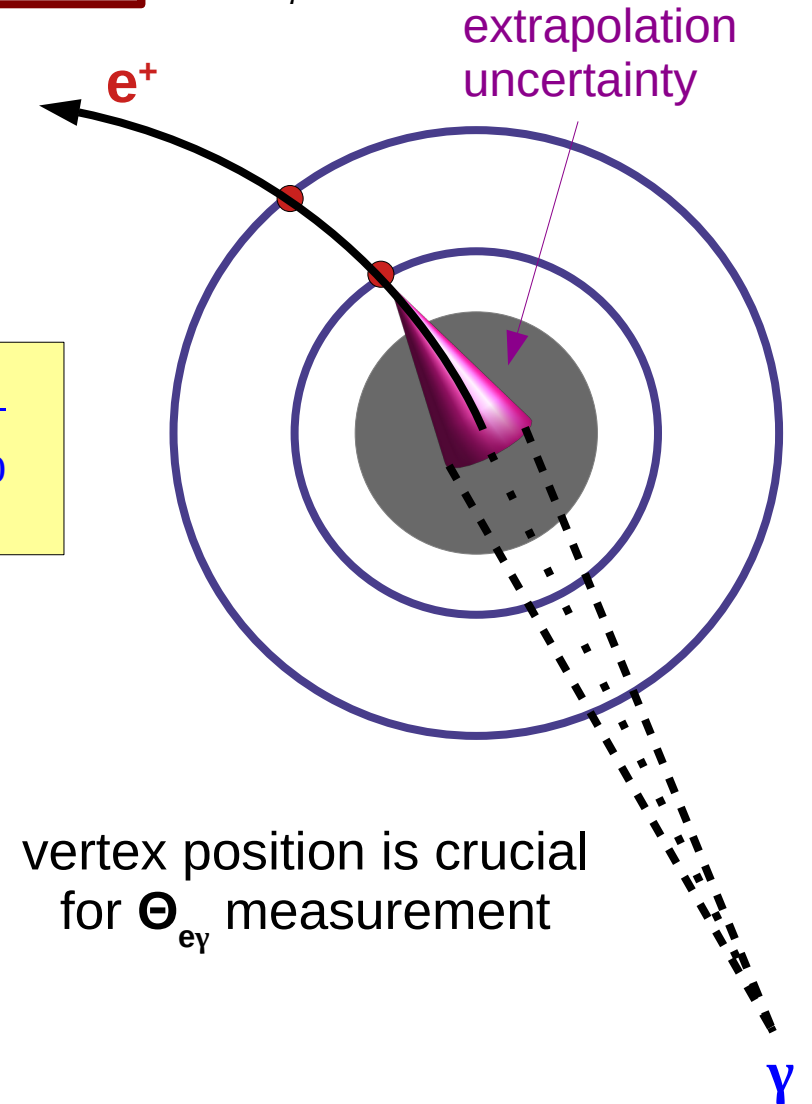
$p_e = 53 \text{ MeV}/c$



we can make the pixels sufficiently small

$$\Theta_{MS} \sim \frac{1}{p} \sqrt{X/X_0}$$

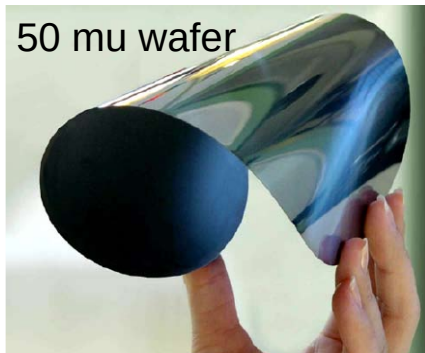
e^+



Thin HVMAPS Vertex Layers

| Pixel sensors | MIMOSA | DEPFET | ALPIDE | HV-MAPS |
|-------------------------------------|----------|--------------|-----------|-----------------|
| TRACKING DETECTOR | STAR PXL | BELLE II PXD | ALICE ITS | Mu3e PTD |
| radiation length per layer in X_0 | 0.5% | 0.2-0.5% | 0.3-0.8% | 0.11% |

Accidental Background scales as: $B_{acc} \propto \sigma(\Theta_{e\gamma})^2 \propto x/X_0$



$p_e = 53 \text{ MeV}/c$:

- 50 μm Si $\rightarrow \sigma(\Theta_e) = 6.0 \text{ mrad}$
- 30 μm Si $\rightarrow \sigma(\Theta_e) = 4.6 \text{ mrad}$

(neglecting multiple scattering in the stopping target)

Remark:
ALICE is also investigating sensors with thickness $< 50 \mu\text{m}$ for ITS III upgrade

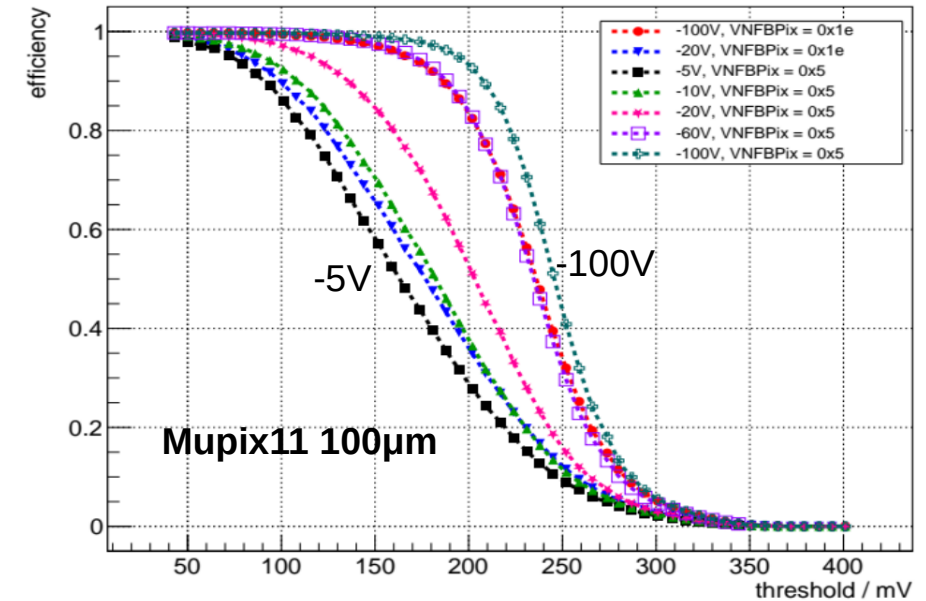
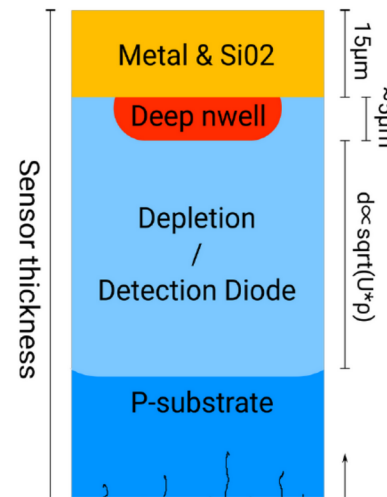
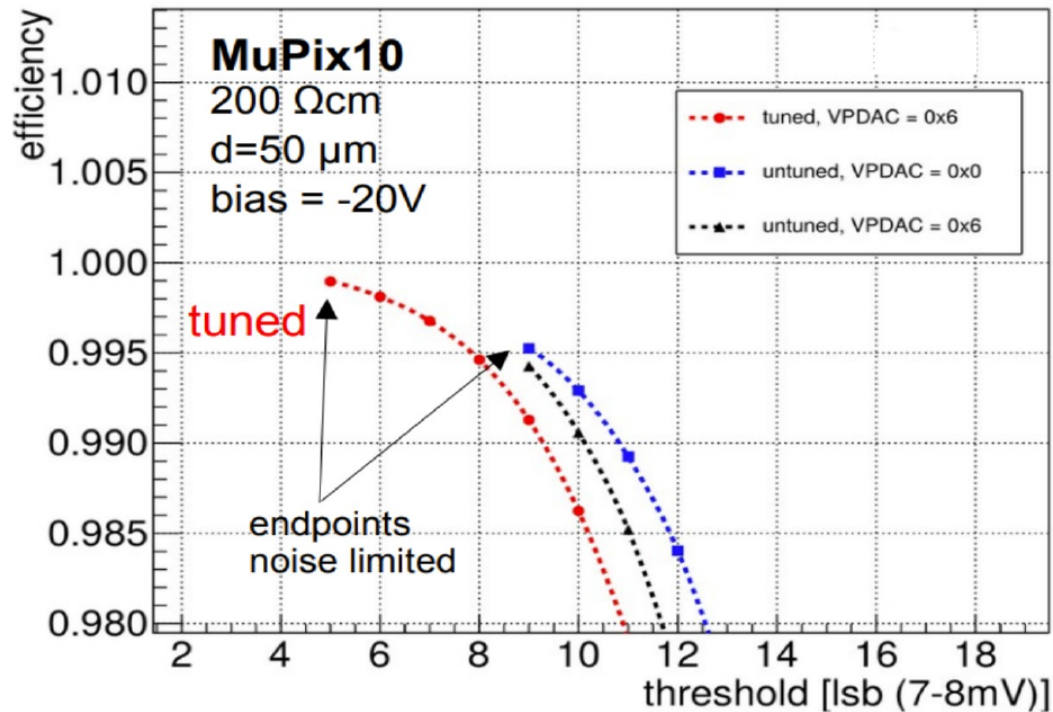
| | Drift Chambers | |
|----------------------------------------------|----------------|--------|
| MEG II TDR | MEG | MEG II |
| $\sigma_{p_{e^+}}^{\text{core}}$ (keV) | 306 | 130 |
| $\sigma_{\theta_{e^+}}^{\text{core}}$ (mrad) | 9.4 | 5.3 |
| $\sigma_{\phi_{e^+}}^{\text{core}}$ (mrad) | 8.7 | 3.7 |

Single Hit Efficiency of thin HVMAPS

Depleted region scales with bias voltage

$$\Delta x_{bias} \propto \sqrt{U \rho}$$

- **Thinner** sensor provides smaller **signal!**
- Goal is to achieve a single **hit eff. > 99.5%**



- **50 μm sensor** → $x_{bias} \sim 30 \mu\text{m}$ → **eff. ~ 99.9%**
- **30 μm sensor** → $x_{bias} \sim 10 \mu\text{m}$ → **eff. ~ 97-98%**

lower threshold possible?

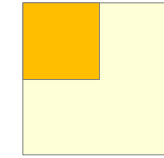
R&D for thin HVMAPS

Detection efficiency depends on signal over noise ratio:

$$\frac{S}{N} \approx \frac{X_{bias}}{C_{pixel}} \approx \frac{X_{bias}}{A_{pixel}}$$

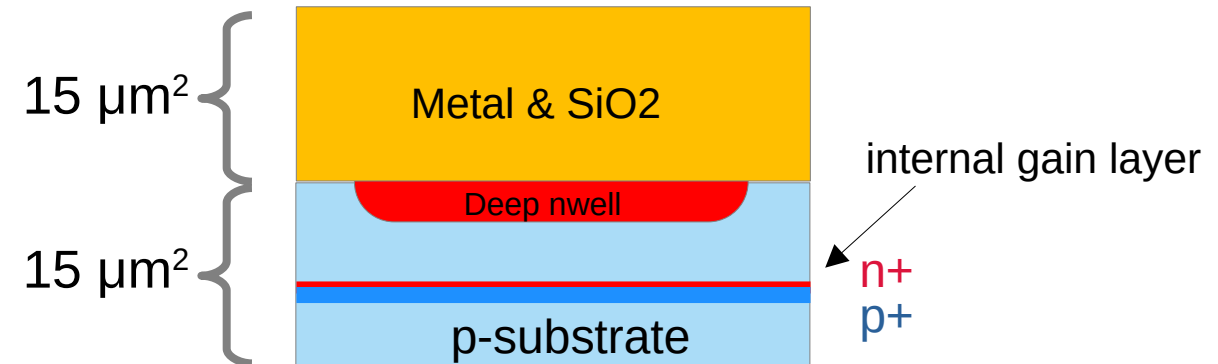
Idea 1:

- make pixel size smaller: $80 \times 80 \mu\text{m}^2 \rightarrow 40 \times 40 \mu\text{m}^2$
- efficiency can be fully restored! \rightarrow higher power density



Idea 2:

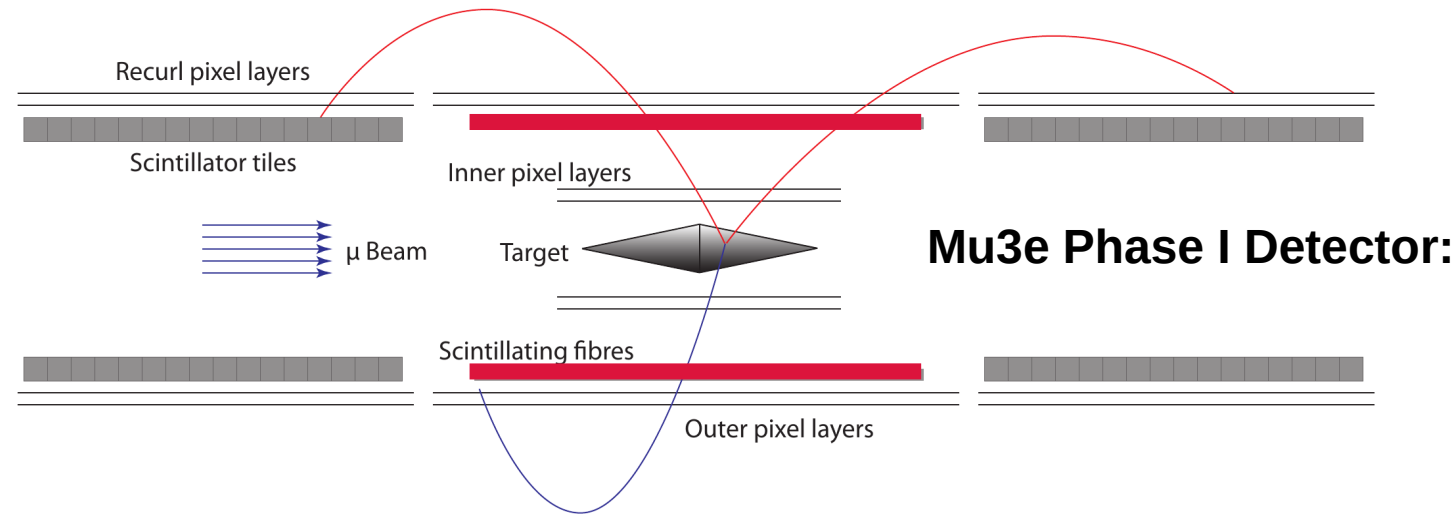
- use design with internal gain layer
- factor 25 internal gain w/o additional power



Plan:

We will test both ideas using the 180nm HVCMOS process from XFAB. First submission planned for 2024

Ultra Fast Silicon Pixel Detector (UFSPD) Motivation



Mu3e Phase I Scintillating Fibres:

- time resolution ~ 250 ps
- rate limit 10^8 μ -stops/s (occupancy & irradiation)
- cannot be used at HIMB rates

Mu3e Phase II

- high beam rate of several 10^9 μ -stops/s
- better time resolution required to suppress acc. BG
- need ultra fast HVMAPS (UFSPD) with time resolution of 100 ps or better

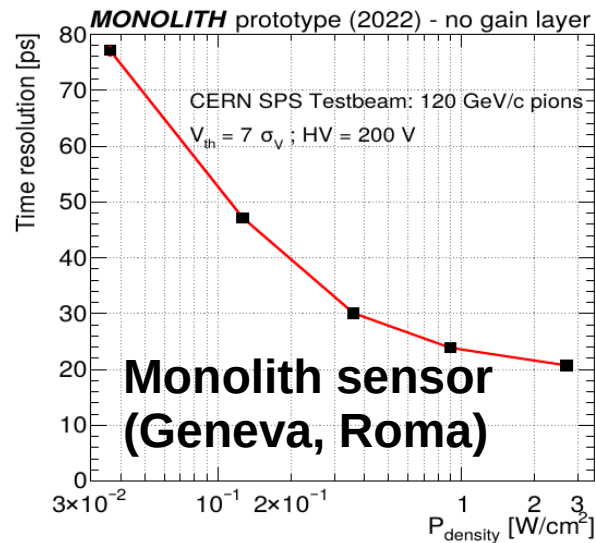
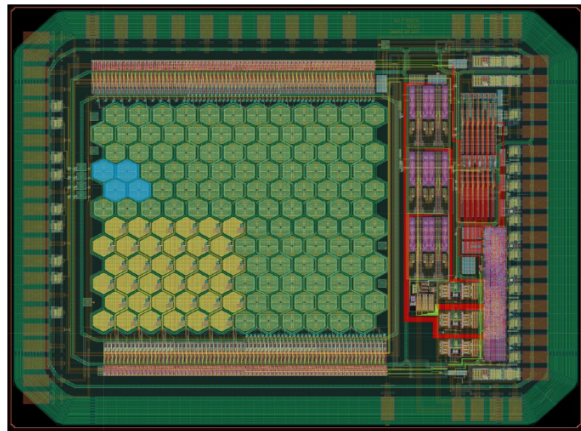


UFSPD Concepts

Sensor without Internal Gain Layer

- IHP 130nm SiGe BiCMOS process
- high cut off frequency (350 GHz)
- use (fast) bipolar transistors for amplifiers and serial drivers

Zambito et al. arXiv:2301.12244



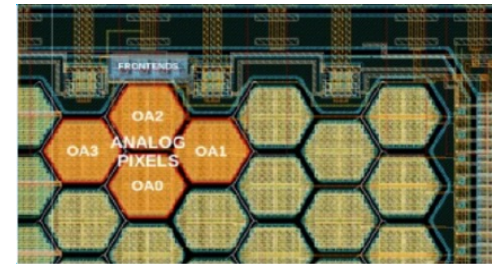
Monolith sensor (Geneva, Roma)

- Best times resolution $\sim 20\text{ps}$
- $P_{\text{density}} = 200 \text{ W}/\text{cm}^2 \rightarrow 40\text{ps}$

Sensor with Internal Gain Layer

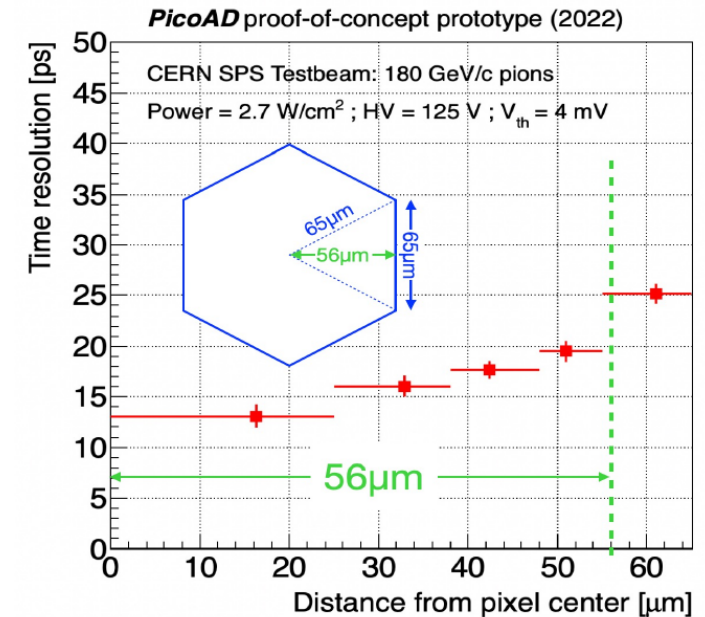
- IHP 130nm SiGe BiCMOS process (option)
- use internal gain layer for fast timing and power saving (ampl. factor ~ 25)

Milanesio et al. NIMA 1046 (2023) 167807



PicoAD sensor (Geneva, Roma)

- Best time resolution $\sim 17\text{ps}$ (unpublished)





Preliminary UFSPD Specification Requirements Mu3e Phase II

Dimensions

Lengths: 40 cm
Radius: 6 cm
Area: 1500 cm²

Rate Assumptions (input)

Myon stopping rate: $2 \cdot 10^9$ /s
Total hit rate in UFSPD: $6 \cdot 10^9$ /s (estimated)

Requirements

Mean hit rate: $4 \cdot 10^6$ /cm²/s
Maximum hit rate: $8 \cdot 10^6$ /cm²/s (estimated)
Max fraction of dead time: 10^{-3}
dead time of pixel: ~300 ns

Pixel size: 200 μm x 200 μm

Time resolution: 100 ps
Max. heat dissipation: 400 mW / cm²

(my personal best guess)

- **Common Mu3e Phase II R&D Project between Geneva, Heidelberg and KIT**
- **Also interesting development for an All-Silicon $\mu^+ \rightarrow e^+ \gamma$ detector**

All Silicon Pixel Tracker for $\mu^+ \rightarrow e^+ \gamma$

$$\frac{N_{acc}}{N_{sig}} \stackrel{\text{def}}{=} B_{acc} \propto R_{\mu} \sigma(p_e) \sigma(E_{\gamma})^2 \sigma(\Theta_{e\gamma})^2 \sigma_{t_{e\gamma}}$$

- **Positron Tracker (incl. Vertex Detector)**

- high rate tolerance (+++)
- good vertex resolution (+++)

- **Ultra-Fast Silicon Pixel Detector (UFSPD)**

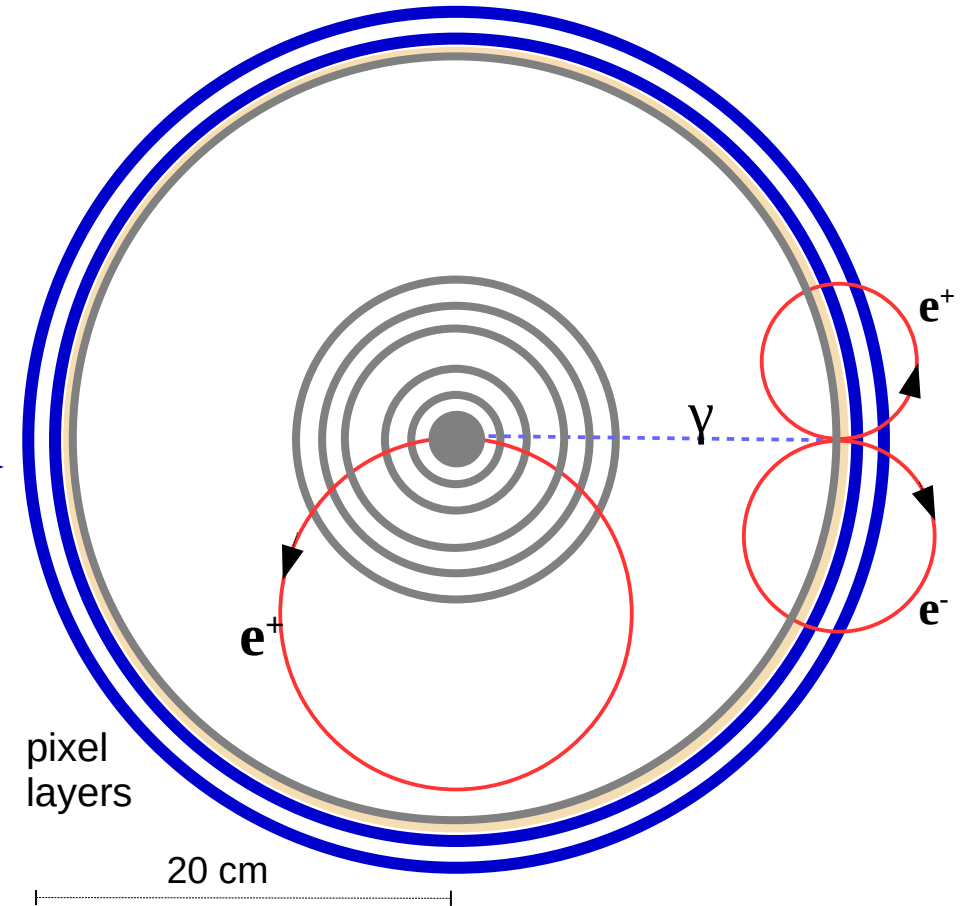
- thin HVMAPS (+++)
- time resolution <100 ps very challenging (---)

- **Converted Photon Tracker**

- high spatial resolution (+++)
- good directional resolution (+++)
- low efficiency (---)

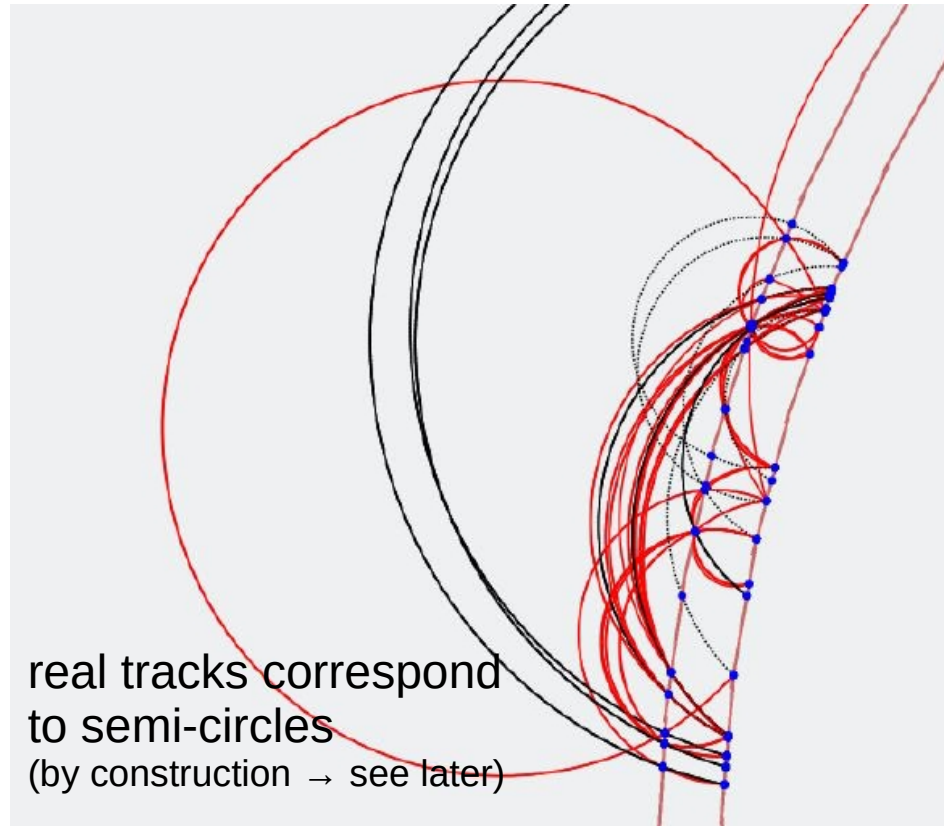
- **Active Muon Stopping Target**

- precise decay vertex (+++)
- technologically challenging (---)



$e^+ e^-$ Track Reconstruction with 2 Pixel Layers

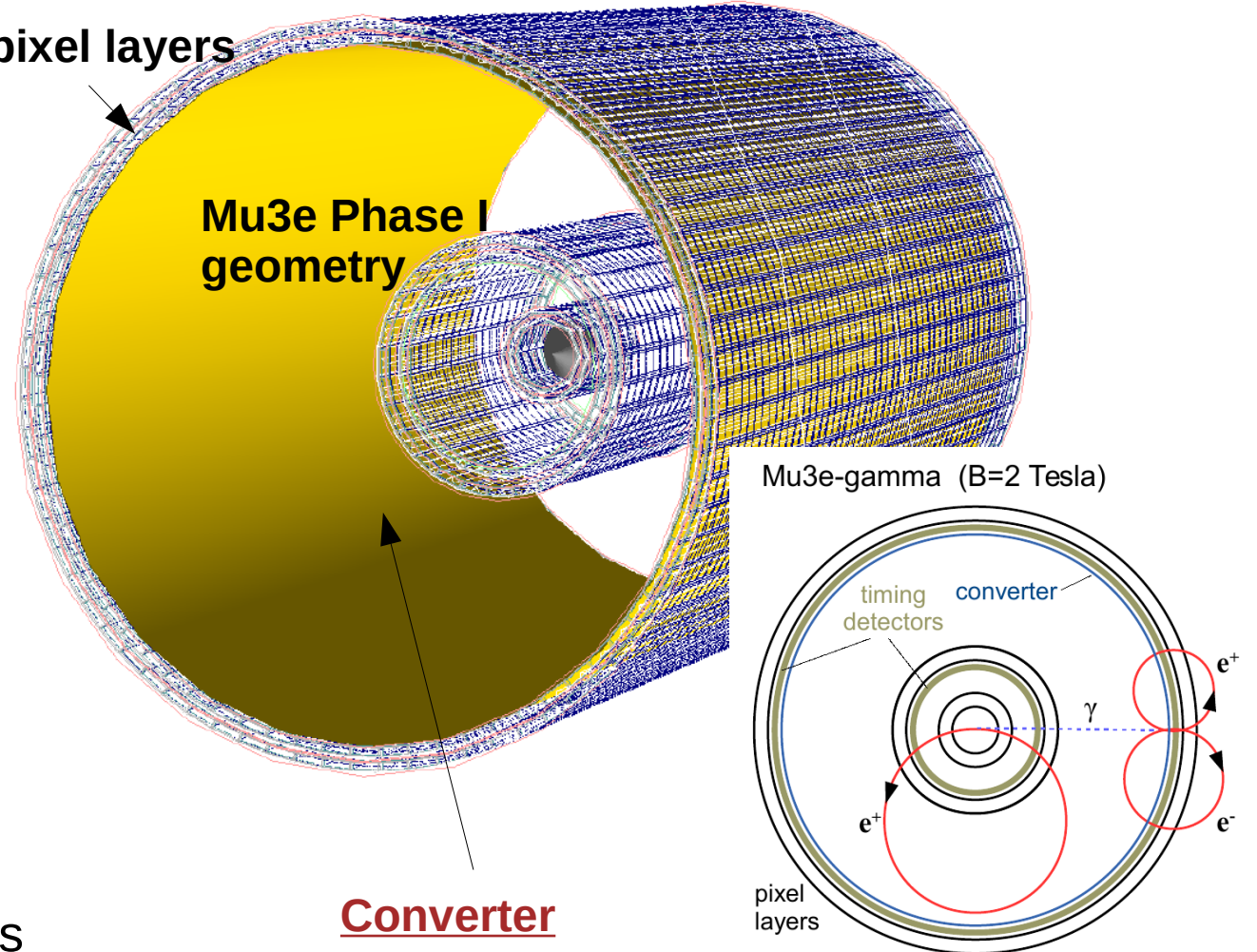
Master Thesis H.Leuschner, Heidelberg, 2019



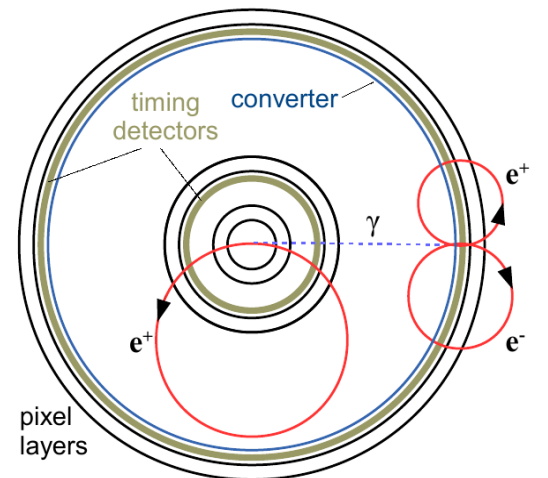
GEANT4 simulation

+2 pixel layers

Mu3e Phase I geometry



Mu3e-gamma (B=2 Tesla)



Converter

- **0.1mm gold**
- **$\sim 3\% X_0$**

Main results of the study:

- high momentum resolution due to small pixels
- two layer tracking of curling tracks works
- proof of concept

Photon Energy Resolution

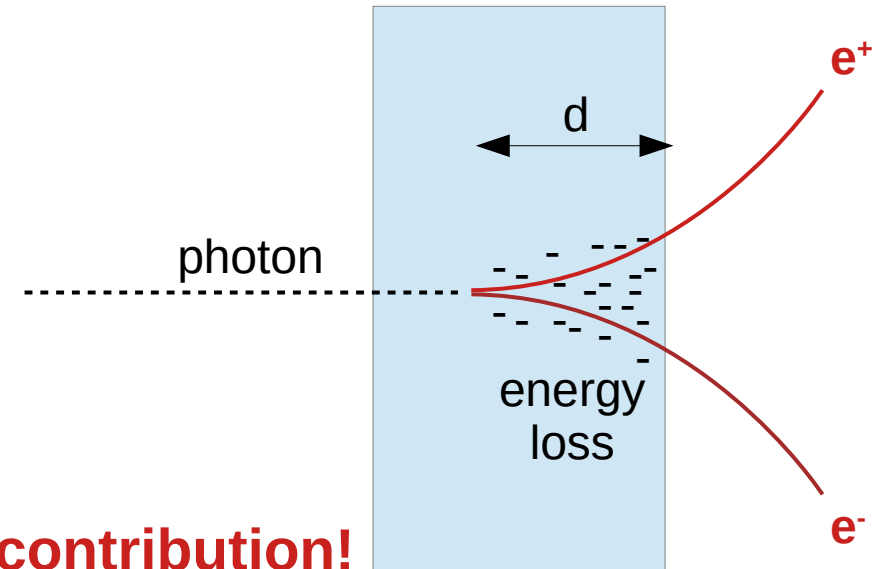
Reconstruction Photon Energy:

$$E_\gamma = p_{ele} + p_{pos} + E_{loss,ele} + E_{loss,pos}$$

Photon Energy Resolution:

$$\sigma(E_\gamma) = \sigma(p_{ele}) + \sigma(p_{pos}) + \sigma(E_{loss,ele}) + \sigma(E_{loss,pos})$$

↙
↘
dominant



Energy loss (ionisation+Brems) in converter is largest contribution!

Ansatz: $\sigma^2(E) \approx 2 \sigma(\text{track}) + \alpha d + \beta d^2$

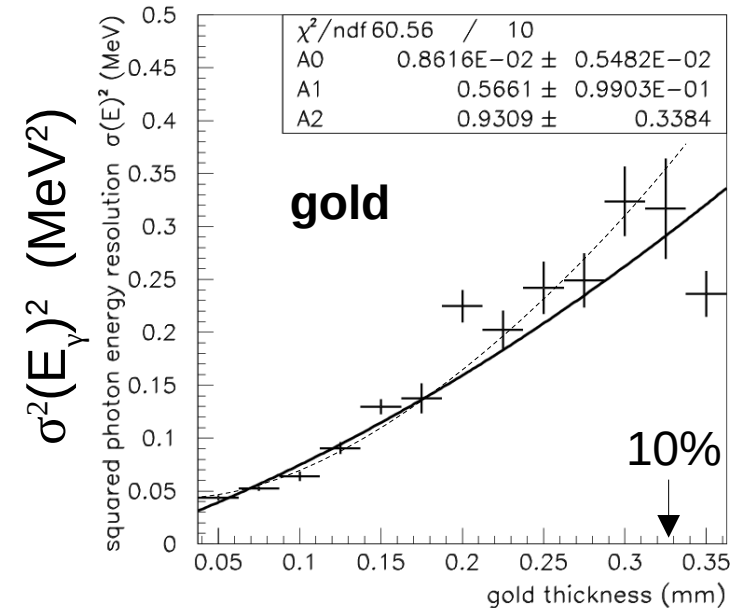
↑
↑
↑

tracking (negligible) **stat.** conversion position uncertainty

energy loss is dominant

Idea:

→ use an Active Silicon Converter (note $E_{crit} \sim 40 \text{ MeV}$)

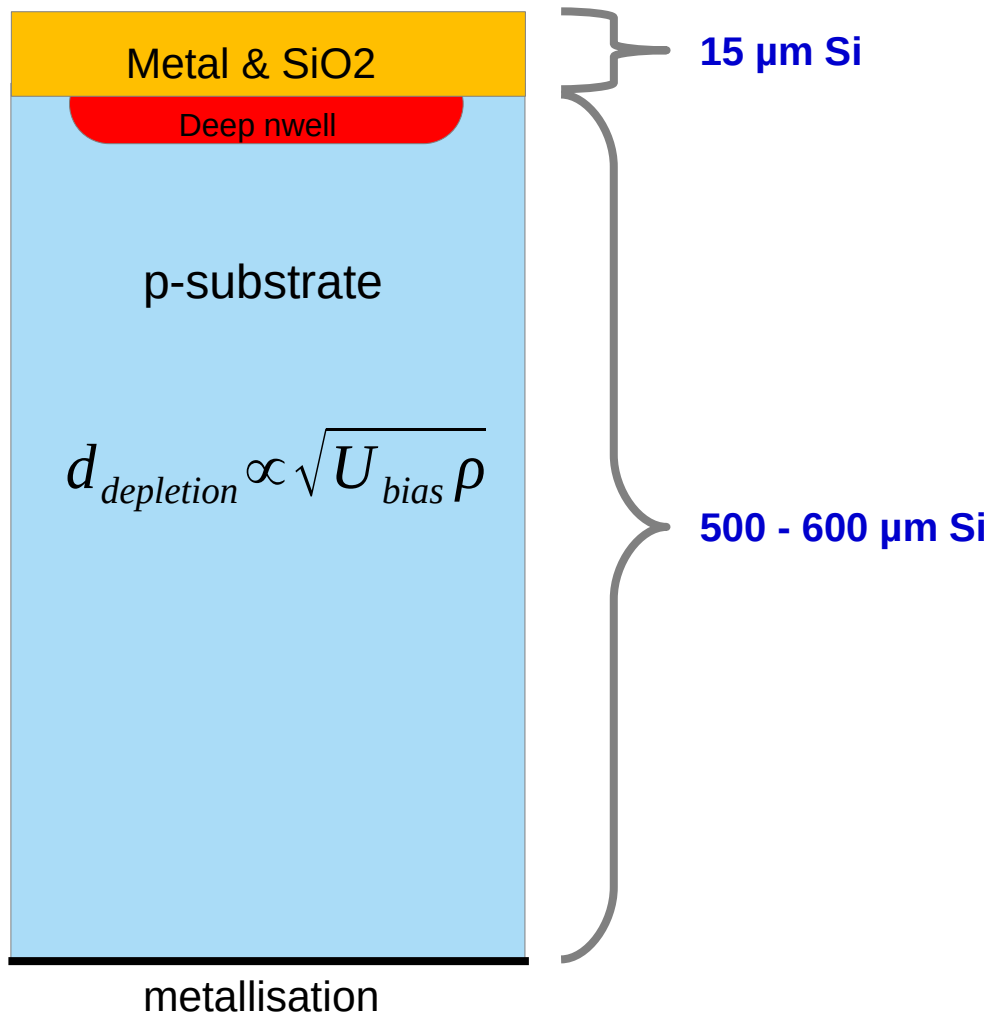


Master thesis H.Leuschner, Heidelberg, 2019

Meeting on Future MEG, 2. October 2024

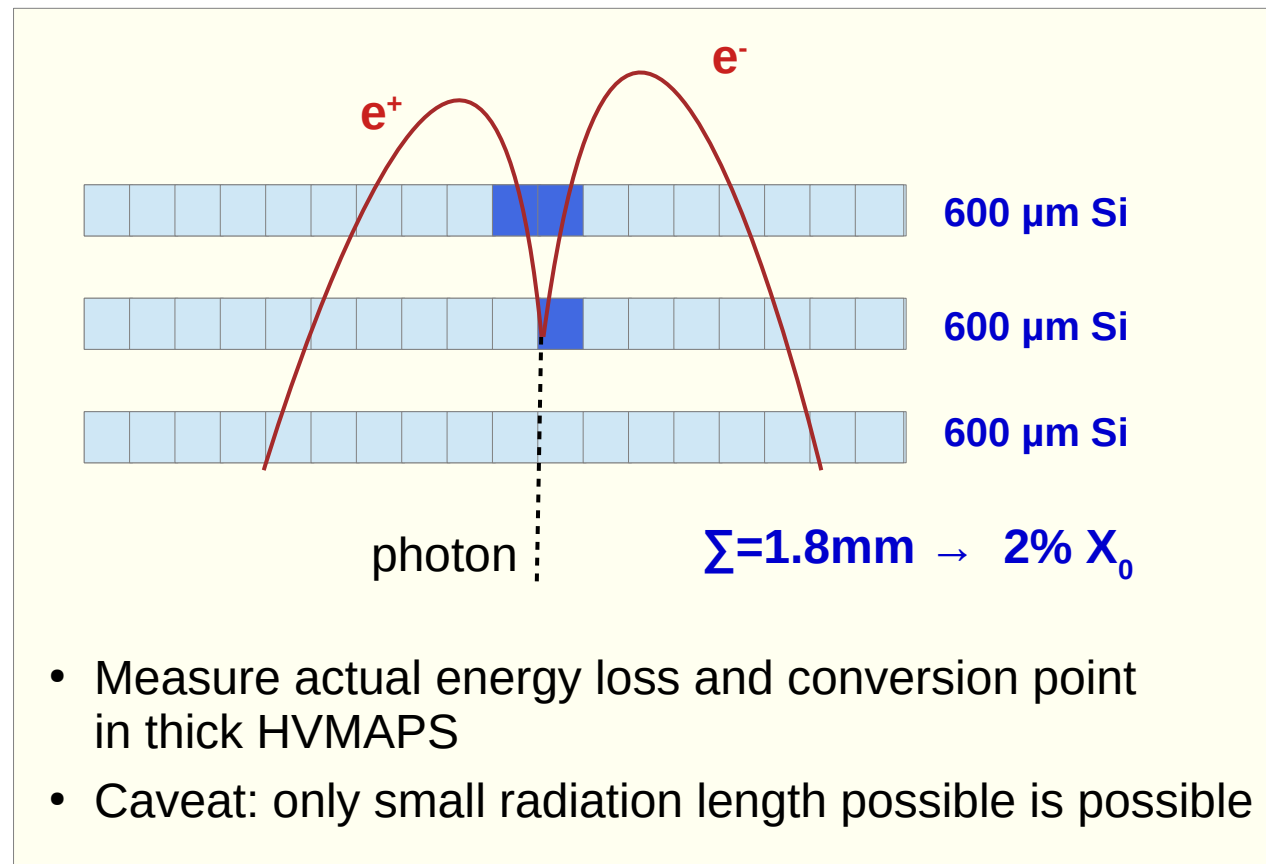


Thick Active HVMAPS Converter Concept



Example:

$$550 \mu\text{m} \approx \sqrt{1000 \text{ V} \cdot 3000 \Omega \text{ cm}}$$



Challenges:

- have to deal with high voltages
- metallisation
- special guard ring structures needed
- first design in 2025 planned

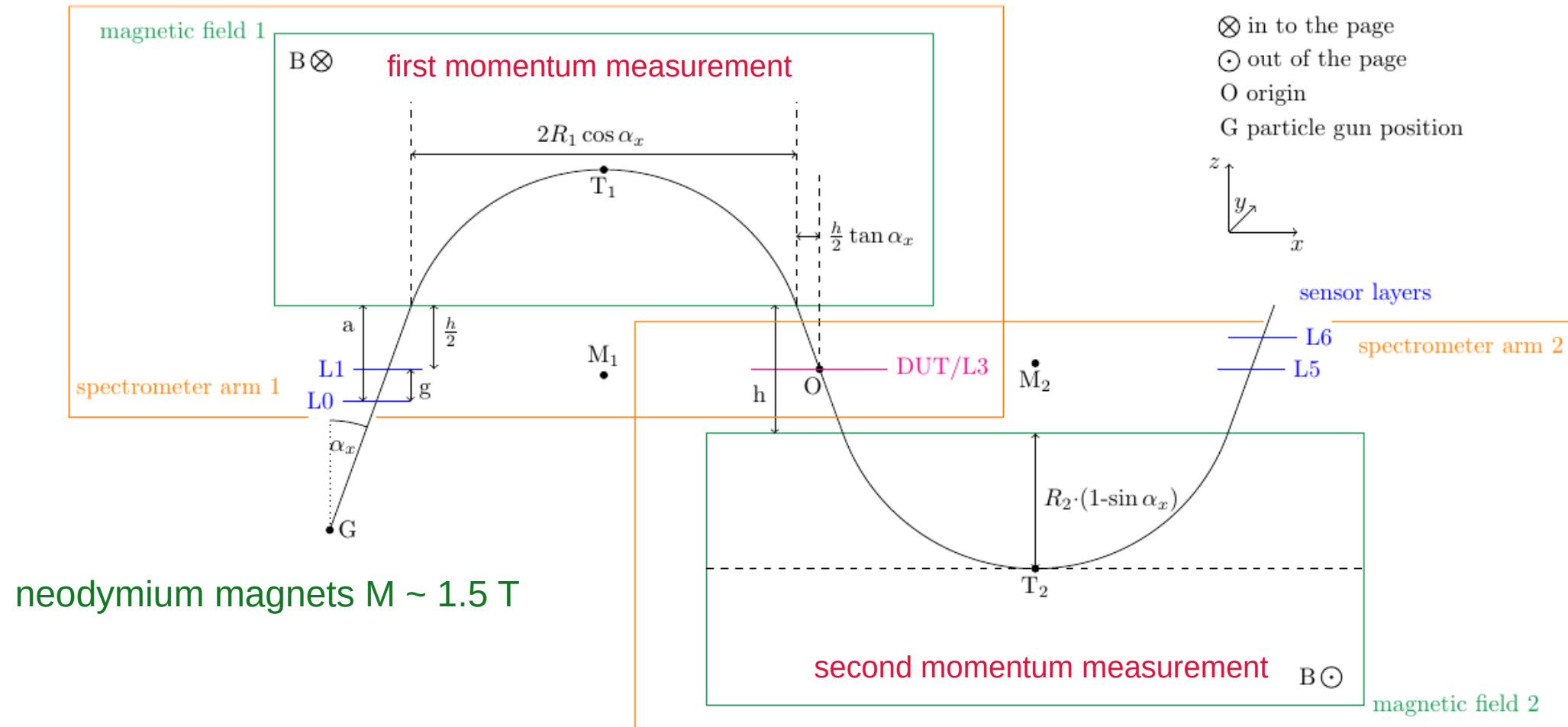


Double Arm Spectrometer Project

(bachelor thesis L.Bees 2024)

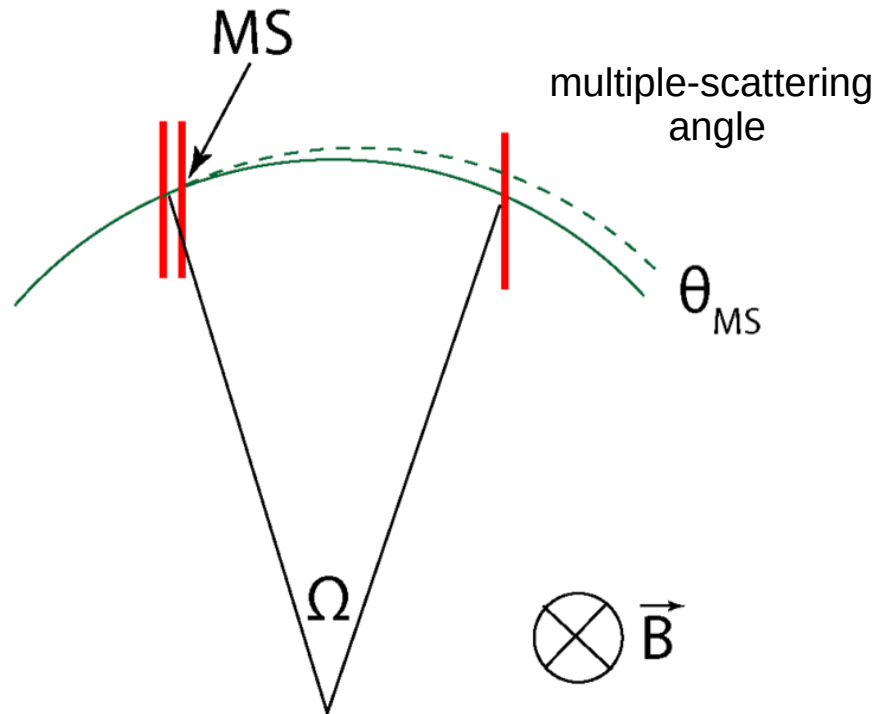
Motivation:

- Energy loss of e^+ / e^- particles in silicon sensors is small ~ 390 keV/mm
- For **sensor characterisation studies** precise reference measurement of **actual energy loss** in DUT is required $\rightarrow \sim 10\text{-}20$ keV



Momentum Resolution

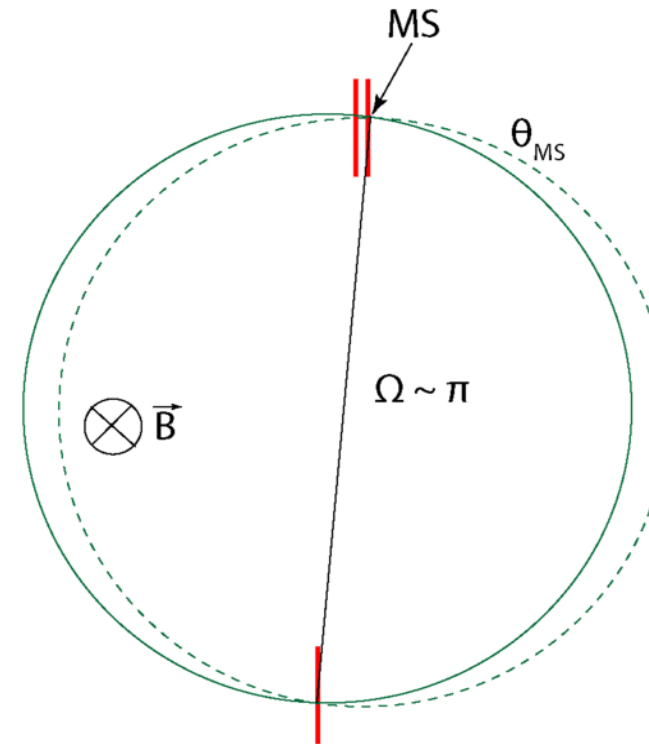
Standard spectrometer:



$$\frac{\sigma_p}{P} \sim \frac{\Theta_{MS}}{\Omega} \quad (\text{linearised})$$

- requires large lever arm
- large bending angle Ω

“Half turn” spectrometer:



$$\frac{\sigma_p}{P} \sim O(\Theta_{MS}^2)$$

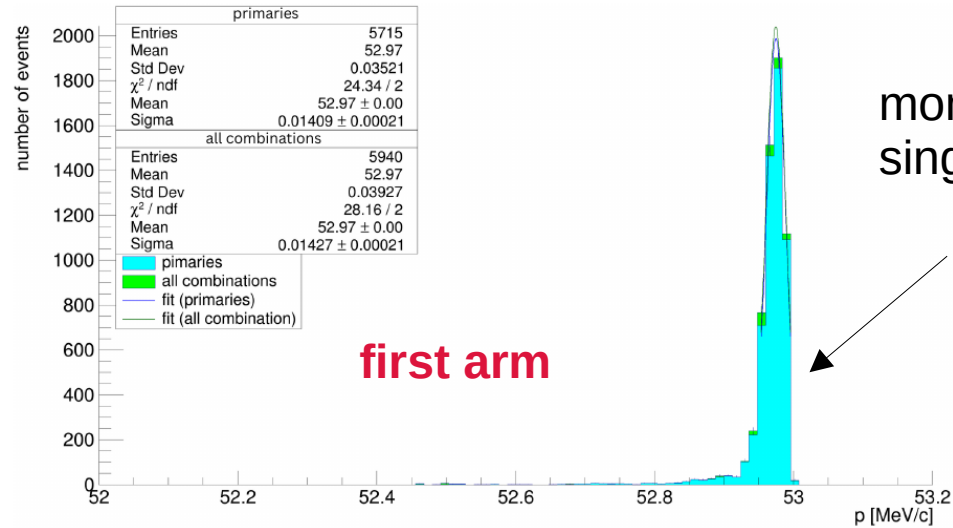
- best precision for **half turn** tracks
- measure **recurlers**



GEANT4 Simulation Results

(bachelor thesis L.Bees 2024)

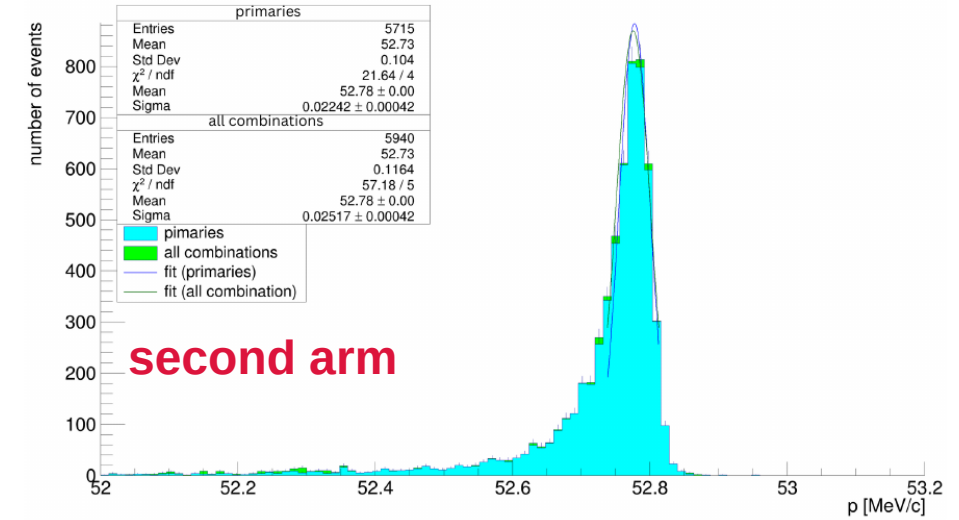
Electron beam with $p=53 \text{ MeV/c}$



first arm

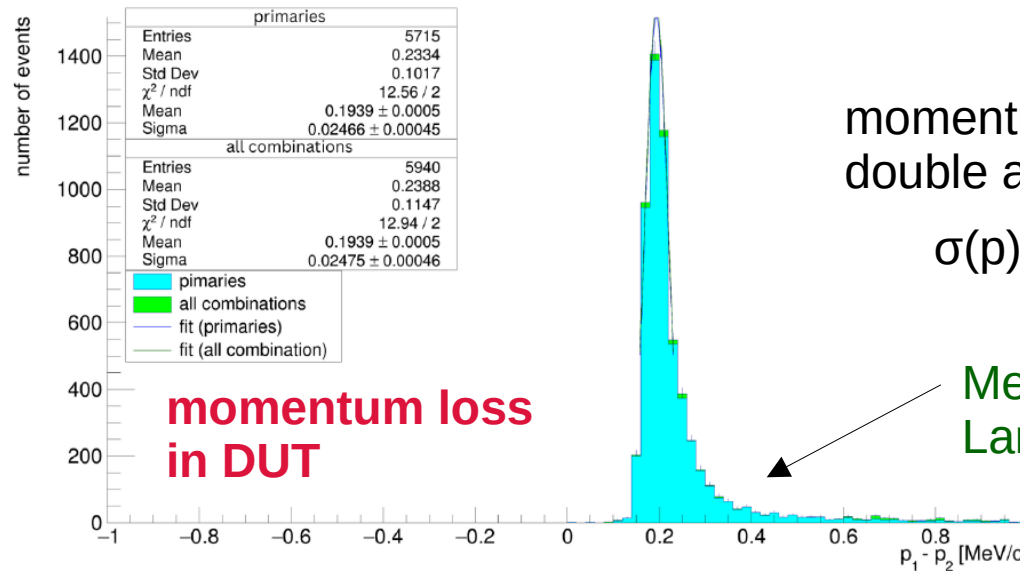
momentum resolution in single arm is about $\sigma(p) \approx 14 \text{ keV/c}$

DUT: 600 μm Si



second arm

Construction of setup is planned for 2025



momentum loss in DUT

momentum loss resolution of double arm setup is about $\sigma(p) \approx 20 \text{ keV/c}$

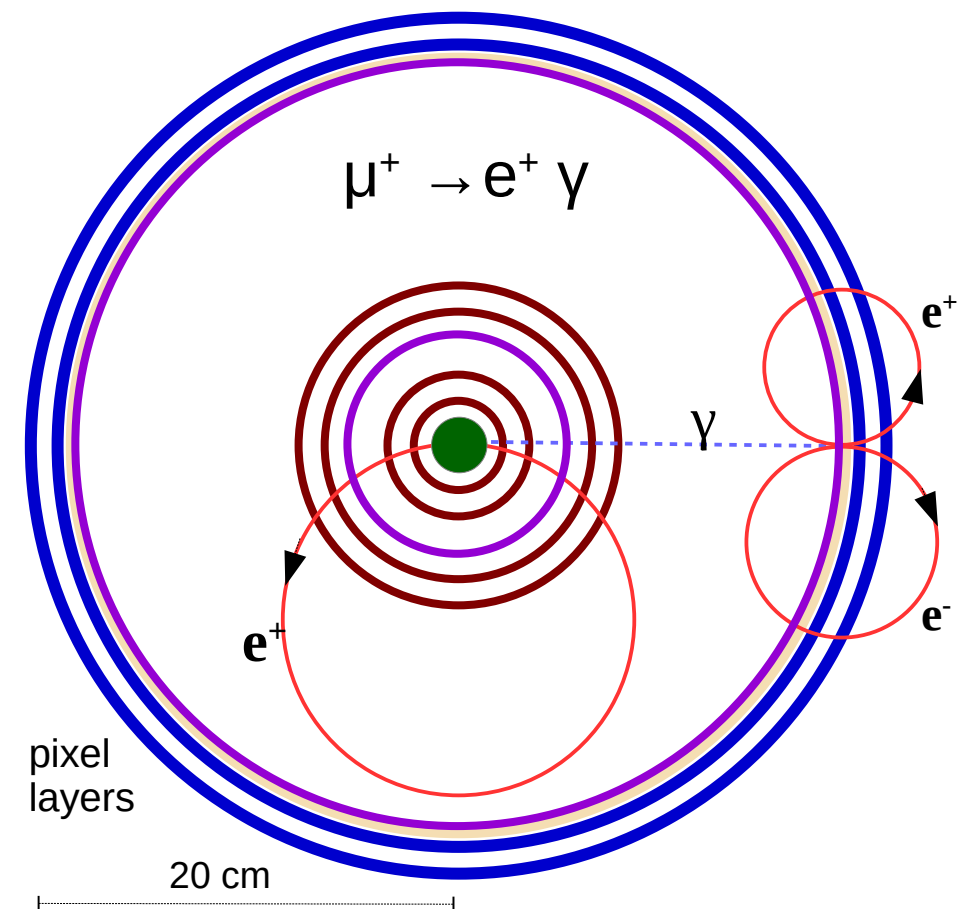
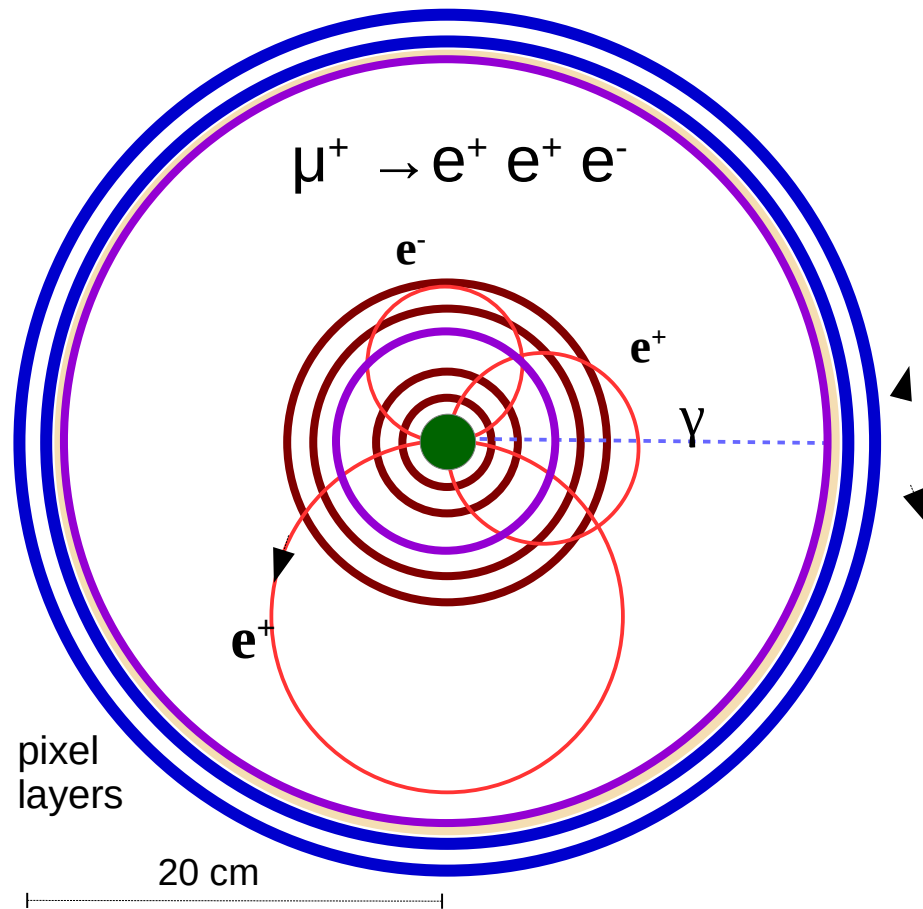
Measurement of Landau tail is possible



Mu3e-Gamma

Question:

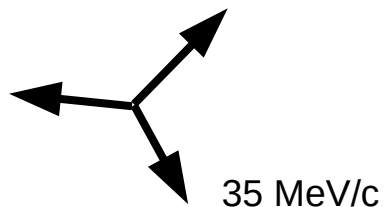
can one combine two experiments Mu3e (Phase II) and search for $\mu^+ \rightarrow e^+ \gamma$?



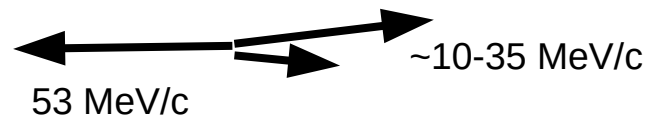


Design Optimisations for Mu3e Phase II

four fermion coupling:



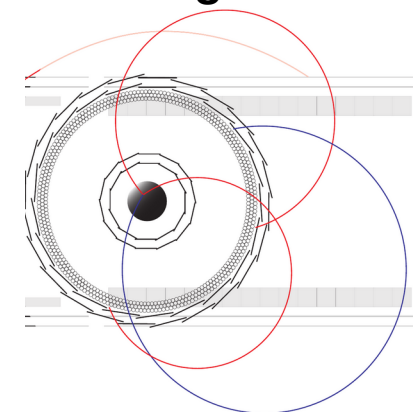
tensor coupling:



radii:

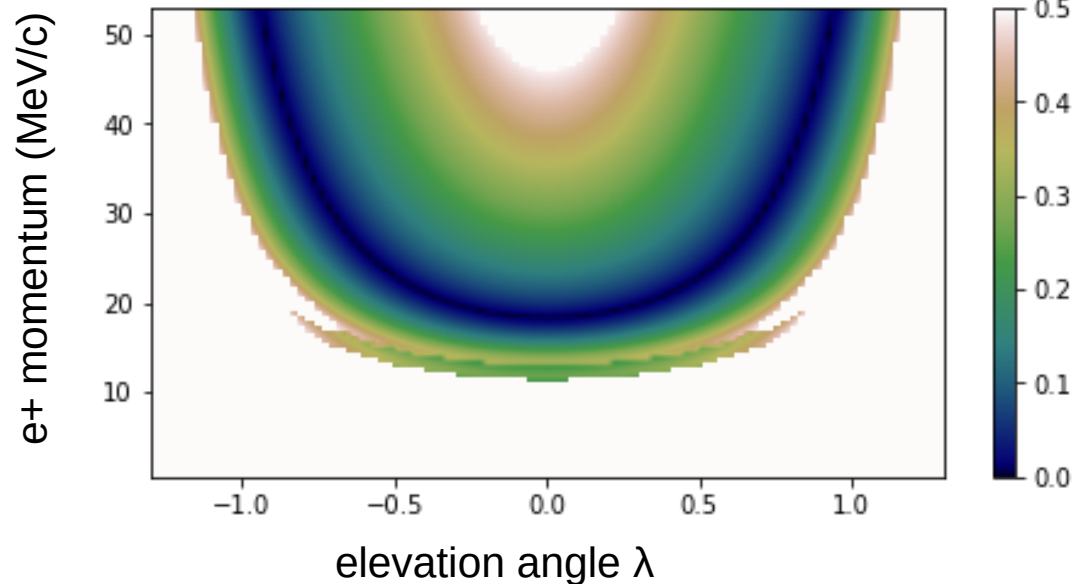
- 23 mm
- 30 mm
- 74 mm
- 86 mm

Phase I Design



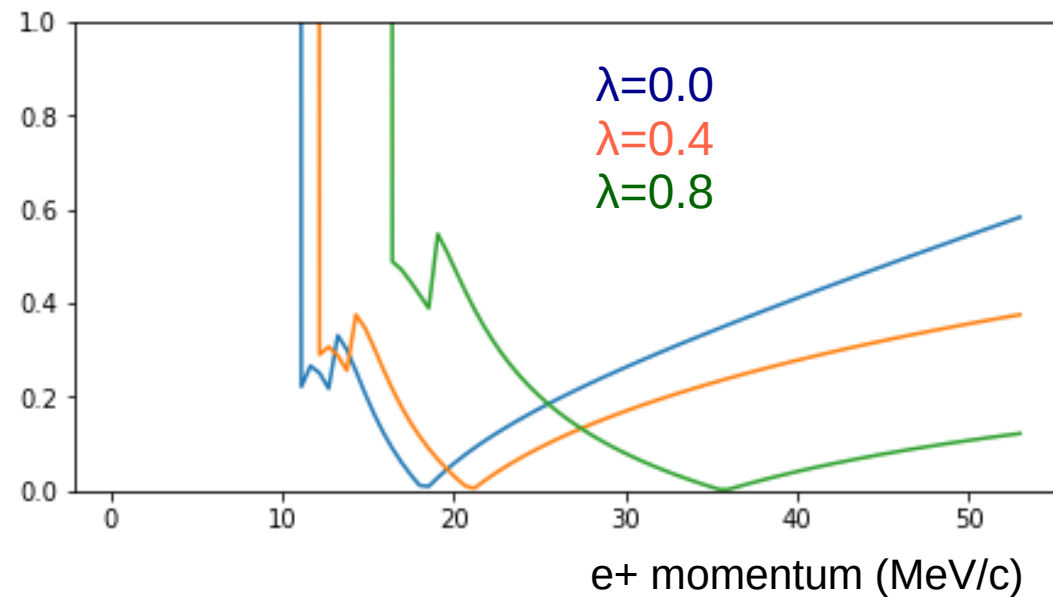
B=1T

e⁺ momentum resolution



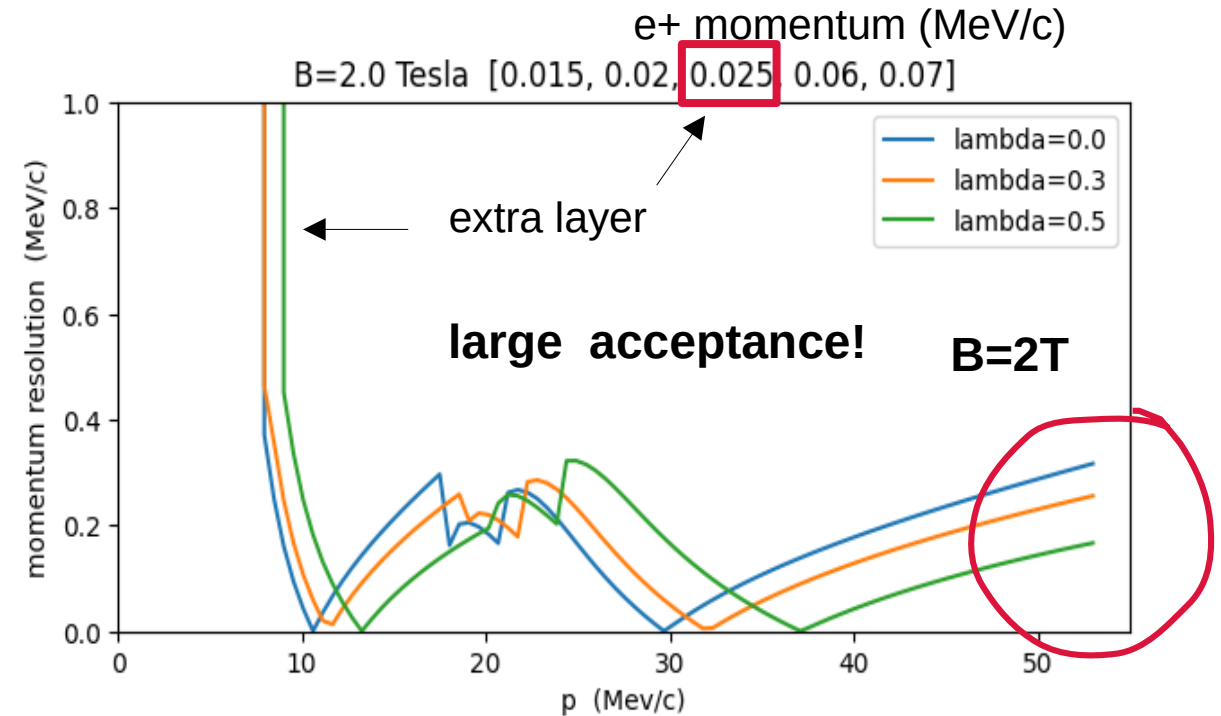
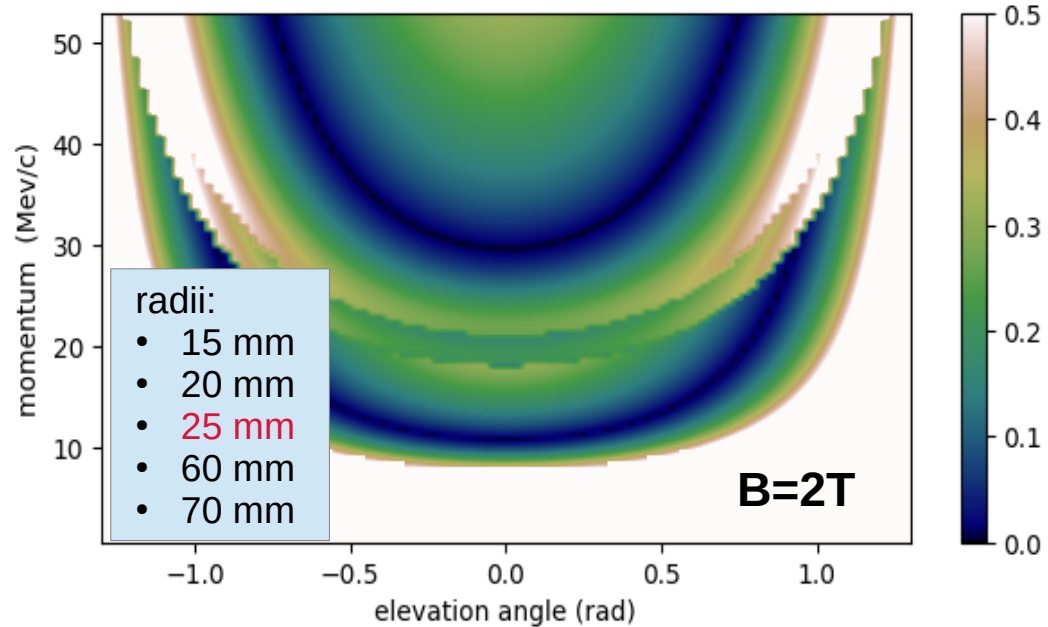
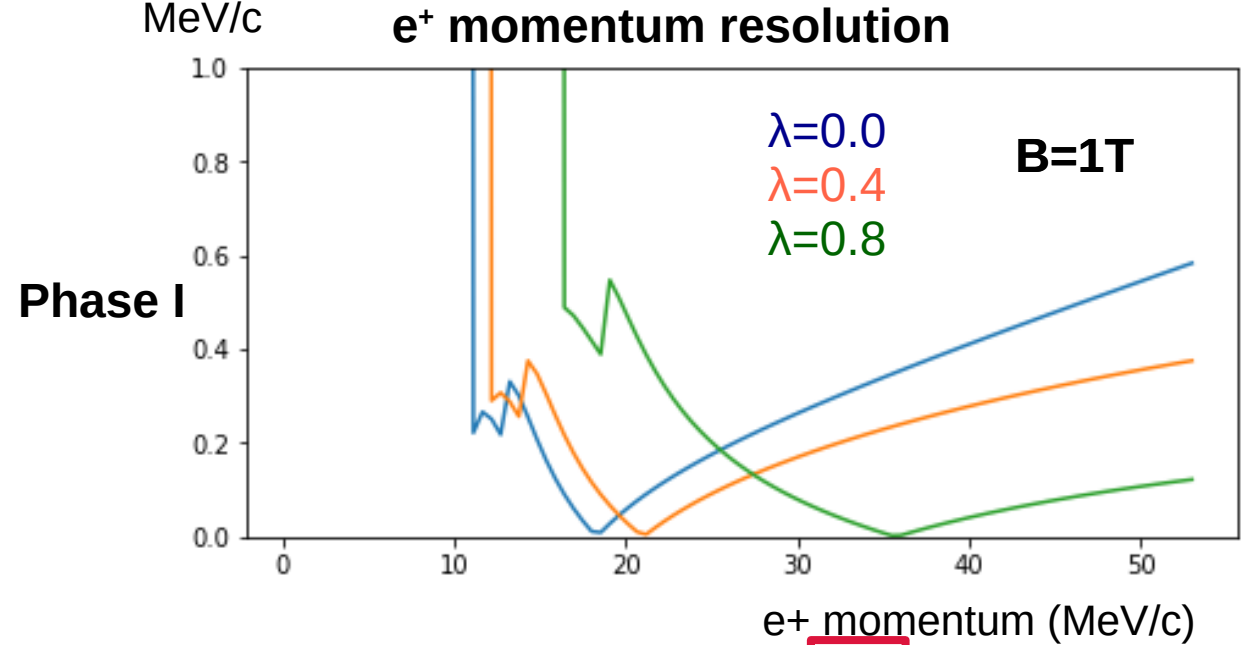
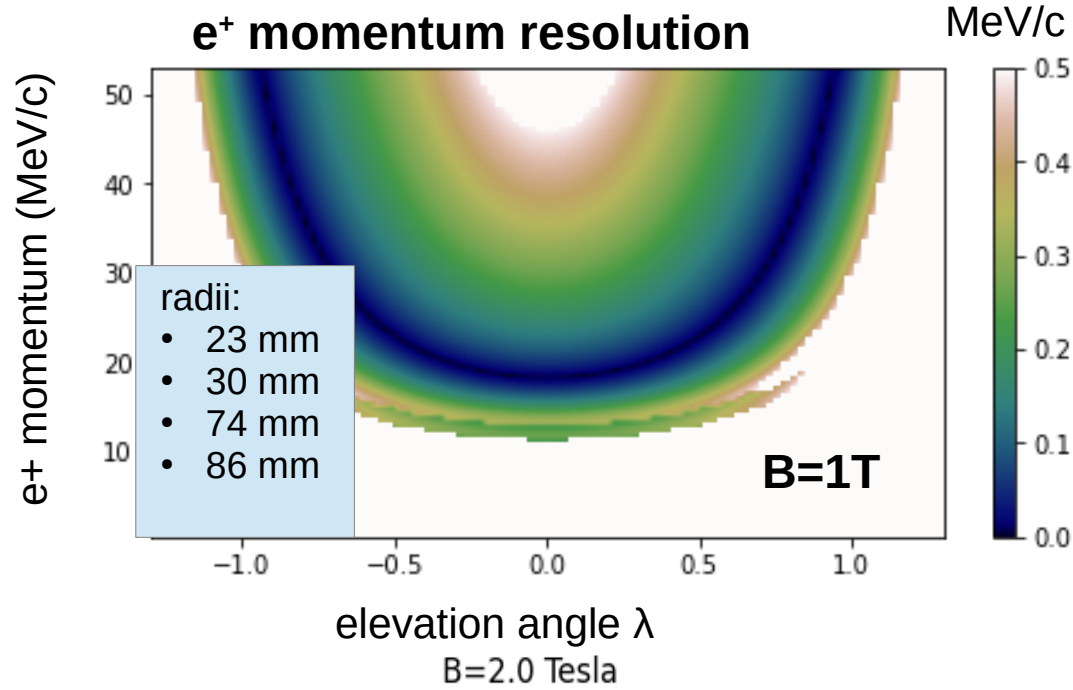
MeV/c

e⁺ momentum resolution



Note: momentum resolution is calculated with multiple scattering model

Design Optimisations for Mu3e Phase II

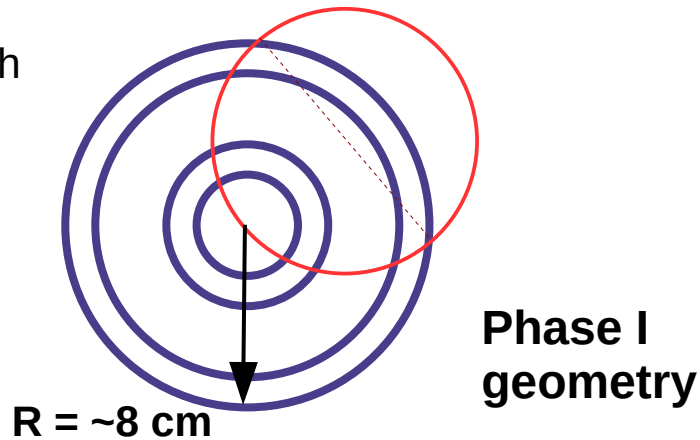


Optimised Solution for $\mu^+ \rightarrow e^+ \gamma$

B = 2.6 Tesla (\rightarrow helps also for the μ -stop rate)

R = 7 cm (pT = 50 MeV/c)

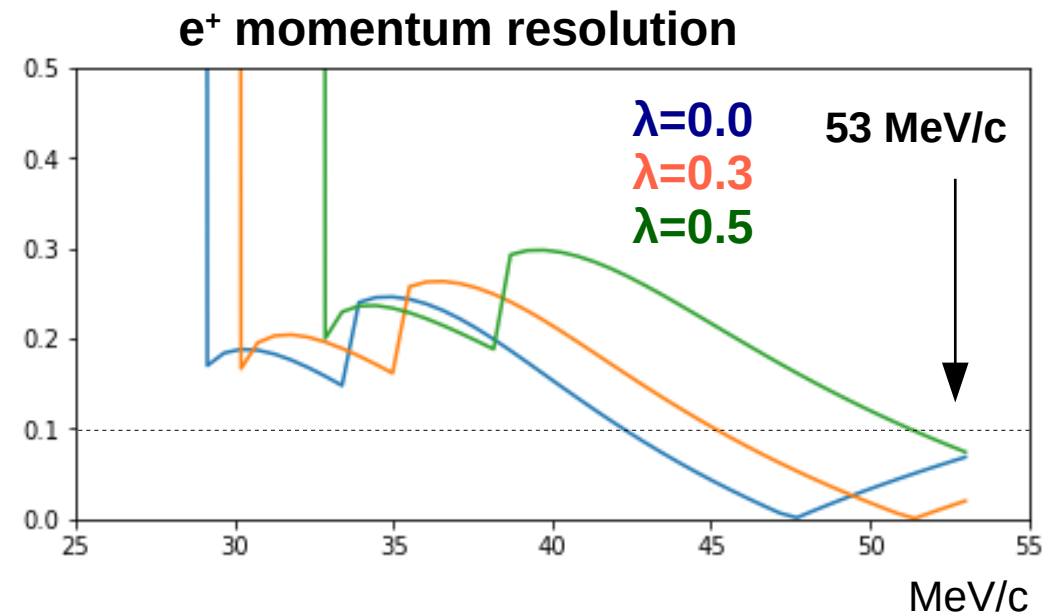
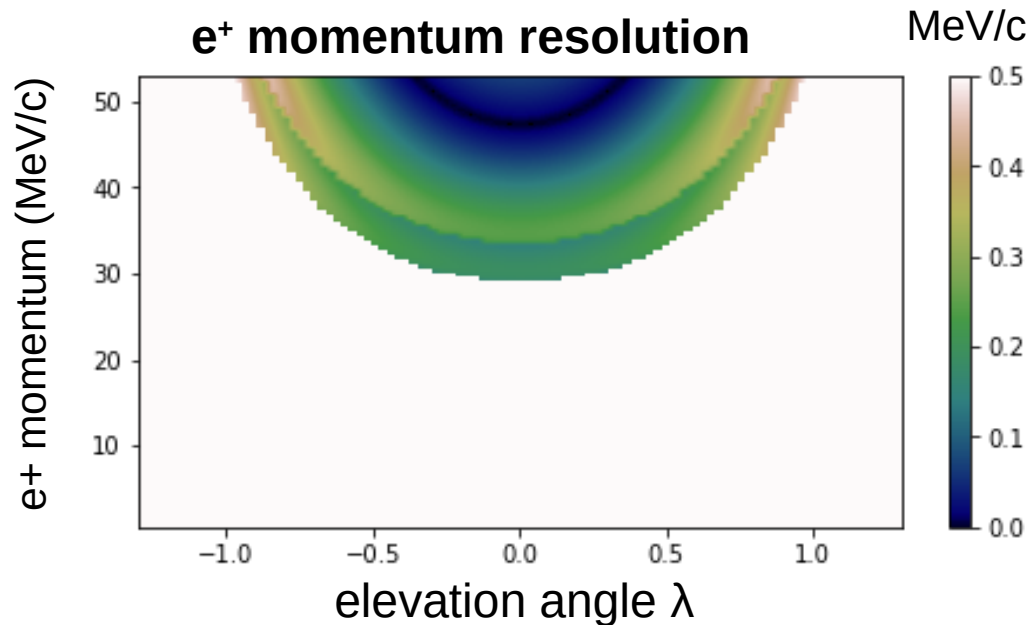
tracking with
4 layers



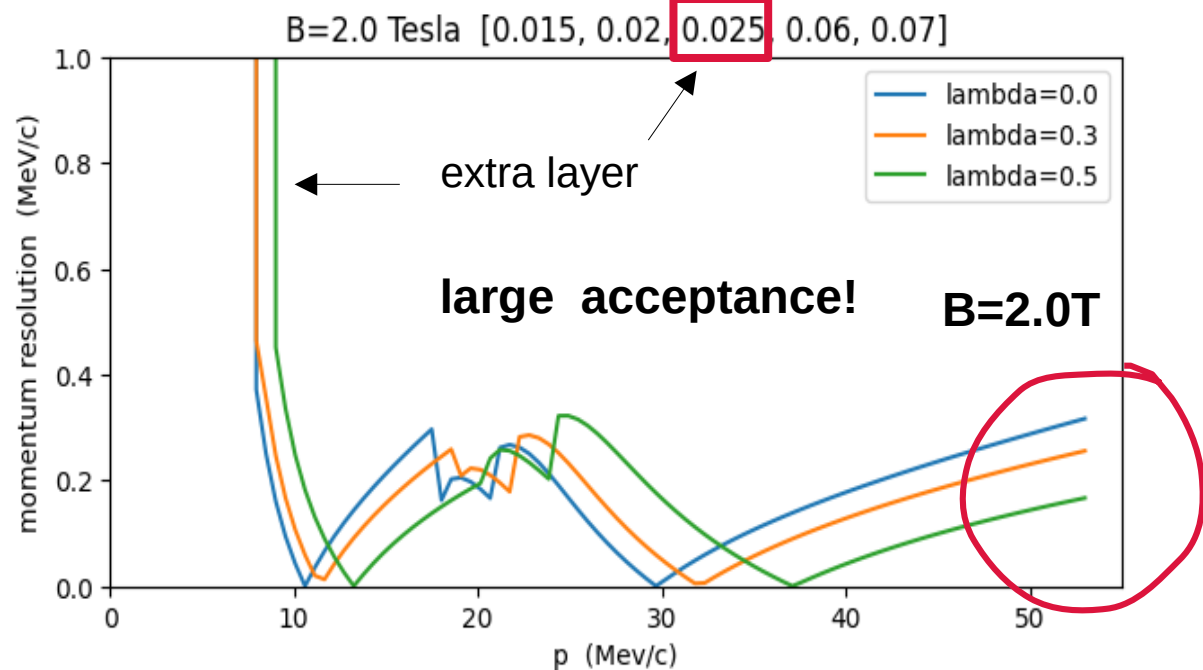
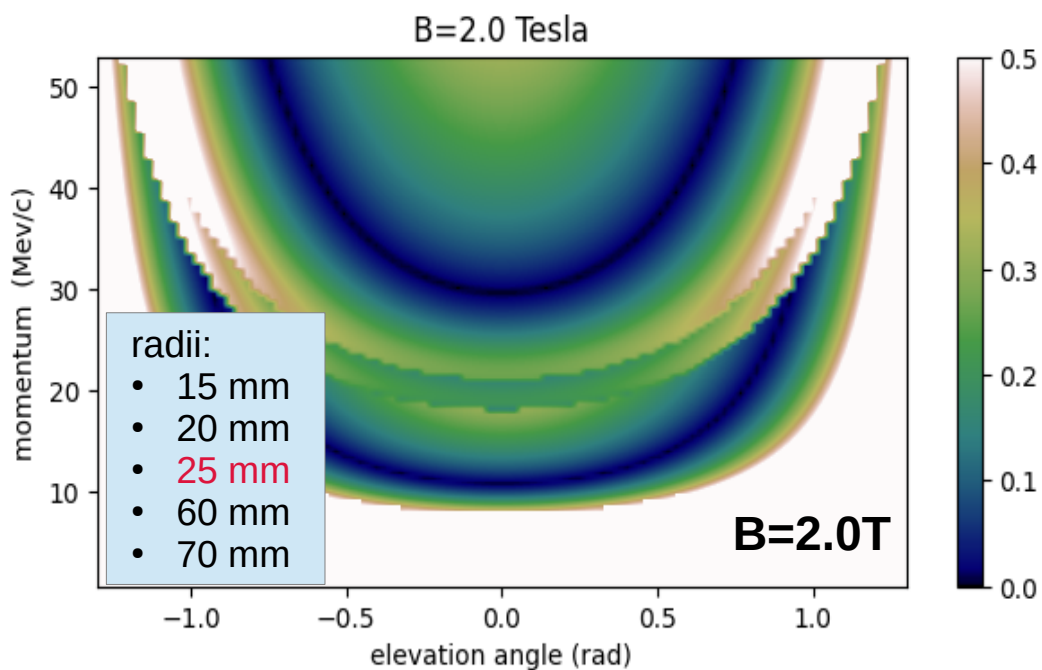
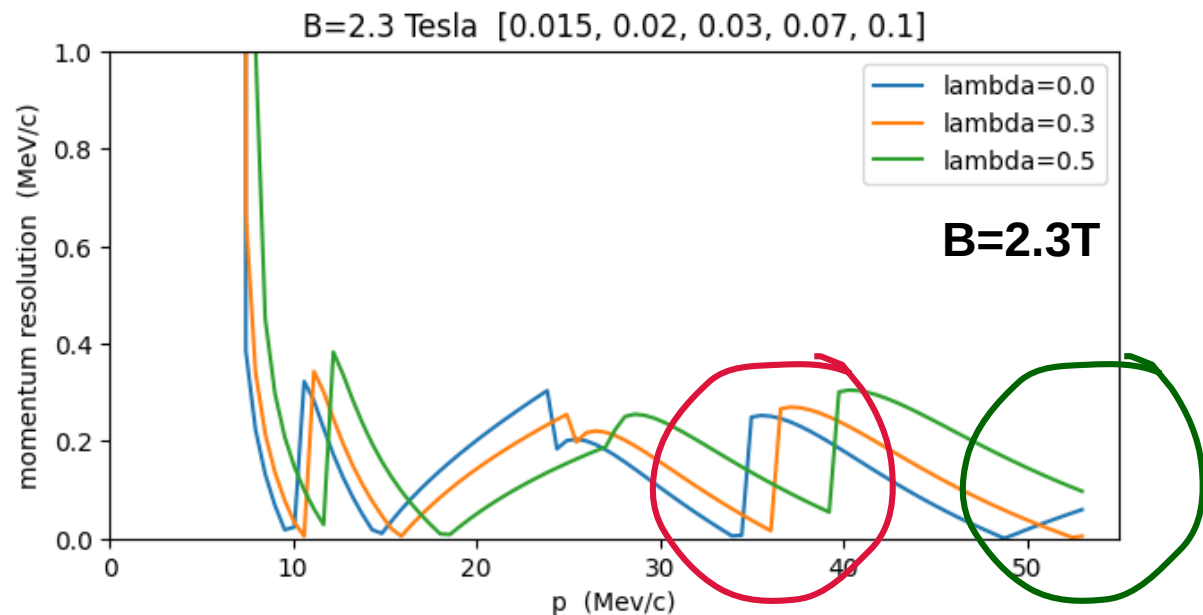
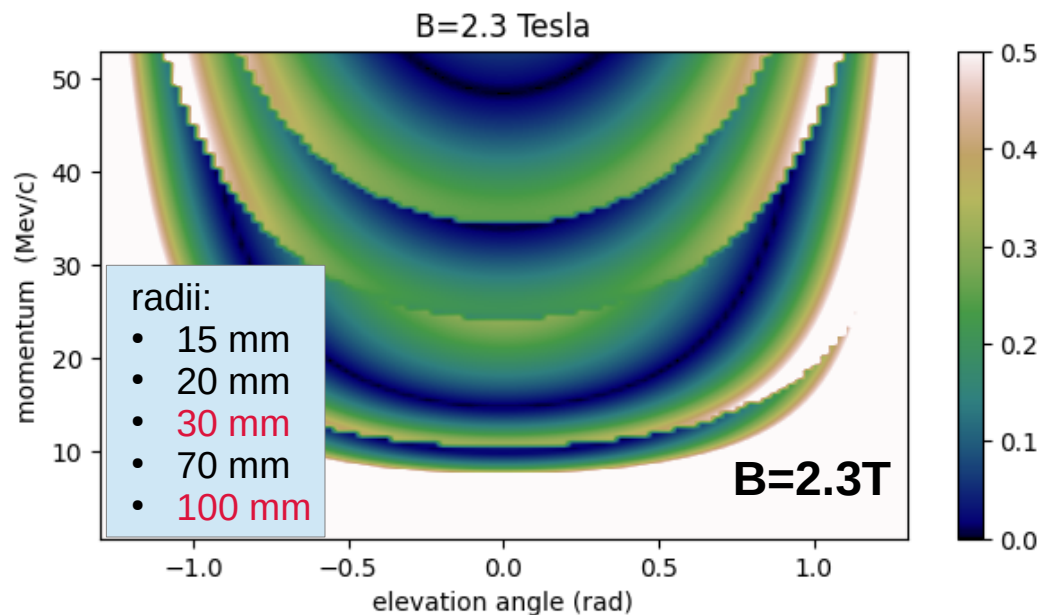
Momentum resolution for half-circles:

- ~12 keV/c from finite pixel size (80 μ m MuPix)
- about 60 keV/c from scattering in **helium** gas (assuming B=2.6T)
- multiple scattering in detector (0.1% X_0) \rightarrow plot

A momentum resolution of about **<80 keV/c** is expected for p=53 MeV/c positrons in the central region $-0.5 < \lambda < 0.5$ by measuring one curl



Study Optimal Mu3e-Gamma Geometry



Summary

Several R&D studies for Mu3e-Gamma performed in Heidelberg

- **Vertexing (also relevant for Mu3e Phase II) :**
 - development of thin HVMAPS (30 μ m)
 - mechanical stability and handling
- **Ultra Fast Silicon Pixel Detector (crucial for Mu3e Phase II)**
 - focus on concept with internal gain layer (\rightarrow save power)
- **Active HVMAPS Converter**
 - requires very thick sensors and high voltage
 - Construction of Double Arm Spectrometer for characterisation studies
- **Design Studies for Mu3e-Gamma:**
 - aiming for optimum momentum resolution in large momentum range
 - and in particular for $p=53$ MeV/c.